

TLE94112ES



Features

- Twelve half bridge power outputs
- Very low power consumption in sleep mode
- 3.3V / 5V compatible inputs with hysteresis
- · All outputs with overload and short circuit protection
- Independently diagnosable outputs (overcurrent, open load)
- Open load diagnostics in ON-state for all high-side and low-side
- Outputs with selectable open load thresholds (HS1, HS2)
- 16-bit Standard SPI interface with daisy chain and in-frame response capability for control and diagnosis
- Fast diagnosis with the global error flag
- PWM capable outputs for frequencies 80Hz, 100Hz and 200Hz with 8-bit duty cycle resolution
- Overtemperature pre-warning and protection
- Over- and Undervoltage lockout
- Cross-current protection

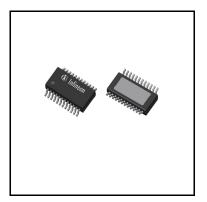
Applications

- HVAC Flap DC motors
- Monostable and bistable Relays
- Side mirror x-y adjustment and mirror fold
- LEDs

Description

The TLE94112ES is a protected twelve-fold half-bridge driver designed especially for automotive motion control applications such as Heating, Ventilation and Air Conditioning (HVAC) flap DC motor control. It is part of a larger family offering half-bridge drivers from three outputs to twelve outputs with direct interface or SPI interface.

The half bridge drivers are designed to drive DC motor loads in sequential or parallel operation. Operation modes forward (cw), reverse (ccw), brake and high impedance are controlled from a 16-bit SPI interface. It offers diagnosis features such as short circuit, open load, power supply failure and overtemperature detection. In combination with its low quiescent current, this device is attractive among others for automotive applications. The small fine pitch exposed pad package, PG-TSDSO-24, provides good thermal performance and reduces PCB-board space and costs.





Туре	Package	Marking
TLE94112ES	PG-TSDSO-24	TLE94112ES

Table 1Product Summary

Normal Operating Voltage	Vs	5.5 18 V
Extended Operating Voltage	Vs	18 20 V
Logic Supply Voltage	V _{DD}	3.0 5.5 V
Maximum Supply Voltage for Load Dump Protection	V _{S(LD)}	40 V
Minimum Overcurrent Threshold	I _{SD}	0.9 A
Maximum On-State Path Resistance at $T_j = 150^{\circ}C$	R _{DSON(total)_HSx+LSy}	1.8 + 1.8 Ω
Typical Quiescent Current at T _j = 85°C	I _{SQ}	0.1 μΑ
Maximum SPI Access Frequency	f _{SCLK}	5 MHz



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Pin Configuration

1 Pin Configuration

1.1 Pin Assignment

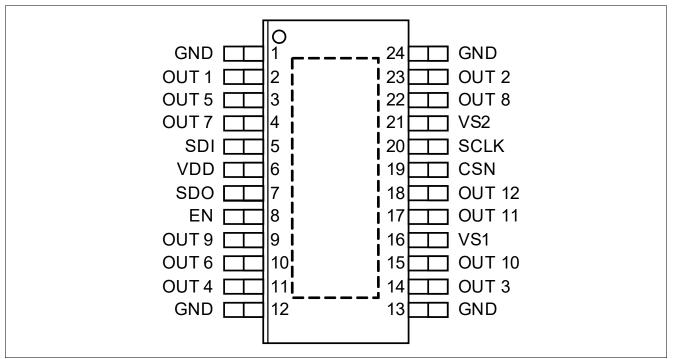


Figure 1 Pin Configuration TLE94112ES

1.2 Pin Definitions and Functions

Pin	Symbol	Function
1	GND	Ground. All ground pins should be externally connected together.
2	OUT 1	Power half-bridge 1
3	OUT 5	Power half-bridge 5
4	OUT 7	Power half-bridge 7
5	SDI	Serial data input with internal pull down
6	VDD	Logic supply voltage
7	SDO	Serial data output
8	EN	Enable with internal pull-down; Places device in standby mode by pulling the EN line Low
9	OUT 9	Power half-bridge 9
10	OUT 6	Power half-bridge 6
11	OUT 4	Power half-bridge 4
12	GND	Ground. All ground pins should be externally connected together.



Pin Configuration

Pin	Symbol	Function
13	GND	Ground. All ground pins should be externally connected together.
14	OUT 3	Power half-bridge 3
15	OUT 10	Power half-bridge 10
16	VS1	Main supply voltage for power half bridges. VS1 should be externally connected to VS2.
17	OUT 11	Power half-bridge 11
18	OUT 12	Power half-bridge 12
19	CSN	Chip select Not input with internal pull up
20	SCLK	Serial clock input with internal pull down
21	VS2	Main supply voltage for power half bridges. VS1 should be externally connected to VS2.
22	OUT 8	Power half-bridge 8
23	OUT 2	Power half-bridge 2
24	GND	Ground. All ground pins should be externally connected together.
EDP	-	Exposed Die Pad; For cooling and EMC purposes only - not usable as electrical ground. Electrical ground must be provided by pins 1,12,13,24. ¹⁾

1) The exposed die pad at the bottom of the package allows better heat dissipation from the device via the PCB. The exposed pad (EP) must be either left open or connected to GND. It is recommended to connect EP to GND for best EMC and thermal performance.



Block Diagram

2 Block Diagram

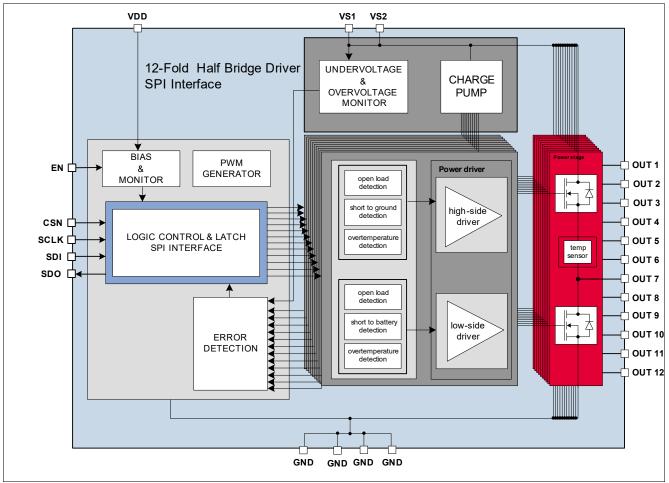


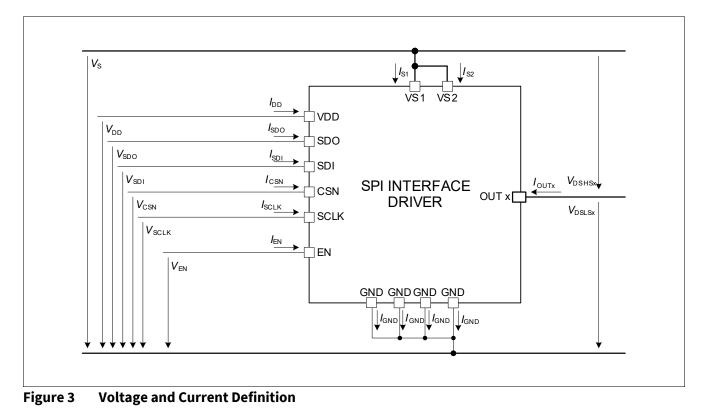
Figure 2 Block Diagram TLE94112ES (SPI Interface)



Block Diagram

2.1 Voltage and current definition

Figure 3 shows terms used in this datasheet, with associated convention for positive values.





3 General Product Characteristics

3.1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings¹⁾ $T_i = -40^{\circ}$ C to +150°C

Parameter	Symbol		Value	S	Unit	Note or	Number	
		Min.	Тур.	Max.		Test Condition		
Voltages		1	1	1	1		- W	
Supply voltage	Vs	-0.3	-	40	V	$V_{\rm S} = V_{\rm S1} = V_{\rm S2}$	P_4.1.1	
Supply Voltage Slew Rate	dV₅/dt	-	-	10	V/µs	V _s increasing and decreasing ¹⁾	P_4.2.2	
Power half-bridge output voltage	V _{OUT}	-0.3	-	40	V	$0 V < V_{OUT} < V_{S}$	P_4.1.2	
Logic supply voltage	V _{DD}	-0.3	-	5.5	V	0 V < V _S < 40 V	P_4.1.3	
Logic input voltages (SDI, SCLK, CSN, EN)	V _{SDI} , V _{SCLK} , V _{CSN} , V _{EN}	-0.3	-	VDD	V	0 V < V _S < 40 V 0 V < V _{DD} < 5.5V	P_4.1.4	
Logic output voltage (SDO)	V _{SDO}	-0.3	-	VDD	V	0 V < V _S < 40 V 0 V < V _{DD} < 5.5V	P_4.1.5	
Currents							L.	
Continuous Supply Current for V _{S1}	I _{S1}	0	-	3.0	А	-	P_4.1.6	
Continuous Supply Current for V _{S2}	I _{S2}	0	-	3.0	А	-	P_4.1.7	
Current per GND pin	I _{GND}	0	-	2.0	А	-	P_4.1.14	
Output Currents	I _{OUT}	-2.0	-	2.0	А	-	P_4.1.15	
Temperatures		·						
Junction temperature	T	-40	-	150	°C	-	P_4.1.8	
Storage temperature	T _{stg}	-50	-	150	°C	-	P_4.1.9	
ESD Susceptibility					-			
ESD susceptibility OUTn and VSx pins versus GND. All other pins grounded.	V _{ESD}	-8	-	8	kV	JEDEC HBM ¹⁾²⁾	P_4.1.10	
ESD susceptibility all pins	V _{ESD}	-2	-	2	kV	JEDEC HBM ¹⁾²⁾	P_4.1.11	
ESD susceptibility all pins	V _{ESD}	-500	-	500	V	CDM ¹⁾³⁾	P_4.1.12	
ESD susceptibility corner pins	V _{ESD}	-750	_	750	V	CDM ¹⁾³⁾	P_4.1.13	

1) Not subject to production test, specified by design

2) ESD susceptibility, "JEDEC HBM" according to ANSI/ ESDA/ JEDEC JS001 (1.5 k Ω , 100pF)

3) ESD susceptibility, Charged Device Model "CDM" according JEDEC JESD22-C101

Notes

1. Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



2. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.



3.2 Functional Range

Table 3Functional Range

Parameter	Symbol		Values	5	Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
Supply voltage range for normal operation	V _{S(nor)}	5.5	-	18	V	-	P_4.2.1
Extended supply voltage range	V _{S(ext)}	18	-	20	V	1)2)	P_4.2.7
Logic supply voltage range for normal operation	V _{DD}	3.0	-	5.5	V	-	P_4.2.3
Logic input voltages (SDI, SCLK, CSN, EN)	V _{SDI} , V _{SCLK} , V _{CSN} , V _{EN}	-0.3	-	5.5	V	-	P_4.2.4
Junction temperature	Tj	-40	-	150	°C		P_4.2.5

1) Not subject to production test, specified by design.

2) In the extended supply range, the device is still functional. However, deviations of the specified electrical characteristics are possible.

Note: Within the normal functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.



3.3 Thermal Resistance

Table 4 Thermal Resistance TLE94112ESTLE94110ES

Parameter	Symbol		Values	5	Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
Junction to Case, $T_A = 85^{\circ}C$	R _{thjC_hot}	-	1.7	-	K/W	1)	
Junction to ambient, $T_A = 85^{\circ}C$ (1s0p, minimal footprint)	R _{thjA_hot_m}	-	77.3	-	K/W	1) 2)	
Junction to ambient, $T_A = 85^{\circ}C$ (1s0p, 300mm2 Cu)	R _{thjA_hot_30}	-	44.9	-	K/W	1) 3)	
Junction to ambient, $T_A = 85^{\circ}C$ (1s0p, 600mm2 Cu)	R _{thjA_hot_60}	-	38.2	-	K/W	1) 1)	
Junction to ambient, $T_A = 85^{\circ}C$ (2s2p)	R _{thjA_hot_2s}	-	26.9	-	K/W	1) 5)	

Specified R_{thJA} value is according to JEDEC JESD51-2, -3 at natural convection on FR4 1s0p board; The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5mm board with additional cooling of 600mm2 copper area and 35μm thickness. Ta = 85°C, each channel dissipates 0.135W.



3.4 Electrical Characteristics

Table 5Electrical Characteristics, $V_s = 5.5 V$ to 18 V, $V_{DD} = 3.0V$ to 5.5V, $T_j = -40^{\circ}$ C to $+150^{\circ}$ C, EN= HIGH,
 $I_{OUTn} = 0 A$; Typical values refer to $V_{DD} = 5.0 V$, $V_s = 13.5 V$ and $T_J = 25^{\circ}$ C unless otherwise
specified; all voltages with respect to ground, positive current flowing into pin (unless
otherwise specified)

Parameter	Symbol		Value	5	Unit	Note or Test Condition	Number
		Min.	Тур.	Max.			
Current Consumption, EN = GN	ID					·	
Supply Quiescent current	I _{SQ}	-	0.5	2	μA	$-40^{\circ}\text{C} \le T_{j} \le 85^{\circ}\text{C}$	P_4.4.1
Logic supply quiescent current	I _{DD_Q}	-	0.1	1	μA	$-40^{\circ}C \le T_{j} \le 85^{\circ}C$	P_4.4.2
Total quiescent current	$I_{SQ} + I_{DD_Q}$	-	0.6	3	μA	$-40^{\circ}C \le T_{j} \le 85^{\circ}C$	P_4.4.3
Current Consumption, EN=HIG	Н						
Supply current	I _S	_	0.5	1	mA	Power drivers and power stages are off	P_4.4.4
Supply current	I _{S_HSON}	-	4.5	9	mA	All high-sides ON ¹⁾	P_4.4.101
Logic supply current	I _{DD}	-	1.5	3	mA	SPI not active	P_4.4.5
Logic supply current	I _{DD_RUN}	-	5	-	mA	SPI 5MHz ³⁾	P_4.4.6
Total supply current	I _S +I _{DD_RUN}	-	5.5	-	mA	SPI 5MHz ³⁾	P_4.4.7
Over- and Undervoltage Locko							
Undervoltage Switch ON voltage threshold	V _{UV ON}	4.25	-	5.25	V	V _s increasing	P_4.4.8
Undervoltage Switch OFF voltage threshold	V _{UV OFF}	4	-	5.0	V	V _s decreasing	P_4.4.9
Undervoltage Switch ON/OFF hysteresis	V _{UV HY}	-	0.25	-	V	$V_{\rm UVON}$ - $V_{\rm UVOFF}$ 3)	P_4.4.10
Overvoltage Switch OFF voltage threshold	V _{OV OFF}	21	-	25	V	V _s increasing	P_4.4.11
Overvoltage Switch ON voltage threshold	V _{OV ON}	20	-	24	V	V _s decreasing	P_4.4.12
Overvoltage Switch ON/OFF hysteresis	V _{ov hy}	-	1	-	V	$V_{\rm OVOFF}$ - $V_{\rm OVON}$ ³⁾	P_4.4.13
V _{DD} Power-On-Reset	V _{DD POR}	2.40	2.70	2.90	V	$V_{\rm DD}$ increasing	P_4.4.14
V _{DD} Power-Off-Reset	V _{DD POffR}	2.35	2.65	2.85	V	V _{DD} decreasing	P_4.4.15
V _{DD} Power ON/OFF hysteresis	V _{DD POR HY}	-	0.05	-	V	$V_{\rm DD POR} - V_{\rm DD POffr}^{3)}$	P_4.4.98
Static Drain-source ON-Resista		de or L	ow-Sid	e)			·
High-Side or Low-Side R _{DSON} (all outputs)	R _{DSON_HB_25C}	-	850	1200	mΩ	I _{OUT} = ±0.5 A; T _j = 25 °C	P_4.4.16
High-Side or Low-Side R _{DSON} (all outputs)	R _{DSON_HB_150}	-	1400	1800	mΩ	$I_{OUT} = \pm 0.5 \text{ A};$ $T_{j} = 150 \text{ °C}$	P_4.4.17



Table 5Electrical Characteristics, $V_s = 5.5 V$ to 18 V, $V_{DD} = 3.0V$ to 5.5V, $T_j = -40^{\circ}$ C to $+150^{\circ}$ C, EN= HIGH,
 $I_{OUTn} = 0 A$; Typical values refer to $V_{DD} = 5.0 V$, $V_s = 13.5 V$ and $T_J = 25^{\circ}$ C unless otherwise
specified; all voltages with respect to ground, positive current flowing into pin (unless
otherwise specified) (cont'd)

otherwise specifie							
Parameter	Symbol	Values			Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
High-Side R _{DSON} (HS1 and HS2 in LED mode)	R _{DSON_HI_HB_} 25C	-	950	1300	mΩ	²⁾ $I_{OUT} = -0.1 \text{ A};$ $T_{j} = 25 \text{ °C}$	P_4.4.18
High-Side R _{DSON} (HS1 and HS2 in LED mode)	R _{DSON_HI_HB_}	-	1500	2000	mΩ	²⁾ / _{OUT} = -0.1 A; T _j = 150 °C	P_4.4.19
Output Protection and Diagno	sis of high-si	de (HS)	chann	els of h	alf-brid	ge output	
HS Overcurrent Shutdown Threshold	I _{SD_HS}	-1.4	-1.1	-0.9	A	See Figure 7	P_4.4.89
Difference between shutdown and limit current	I _{LIM_HS} - I _{SD_HS}	-1.2	-0.6	0	A	³⁾ $ I_{\text{LIM}_{HS}} \ge I_{\text{SD}_{HS}} $ See Figure 7	P_4.4.21
Overcurrent Shutdown filter time	t _{dSD_HS}	15	19	23	μs	3)	P_4.4.22
Open Load Detection Current	I _{OLD1_HS}	-15	-8	-3	mA	-	P_4.4.23
Open Load Detection filter time	t _{old1_HS}	2000	3000	4000	μs	3)	P_4.4.24
Open Load Detection Current for LED mode (HS1 & HS2)	I _{OLD2_HS1,2}	-3.2	-2	-0.5	mA	Bit OL_SEL_HS1 = 1, OL_SEL_HS2 = 1	P_4.4.25
Open Load Detection filter time for LED mode (HS1 & HS2)	t _{old2_Hs1,2}	100	200	300	μs	Bit OL_SEL_HS1 = 1, OL_SEL_HS2 = 1; 3)	P_4.4.26
Output Protection and Diagno	sis of low-sid	le (LS)	channe	ls of ha	lf-bridg	e output	
LS Overcurrent Shutdown Threshold	I _{SD_LS}	0.9	1.1	1.4	A	Figure 8	P_4.4.104
Difference between shutdown and limit current	I _{LIM_LS} - I _{SD_LS}	0	0.6	1.2	A	³⁾ $I_{\text{LIM}_{\text{LS}}} \ge I_{\text{SD}_{\text{LS}}}$ Figure 8	P_4.4.28

Overcurrent Shutdown filter time	$t_{\rm dSD_LS}$	15	19	23	μs	3)	P_4.4.29
Open Load Detection Current	I _{OLD_LS}	3	8	15	mA	-	P_4.4.30
Open Load Detection filter time	t _{old_ls}	2000	3000	4000	μs	3)	P_4.4.31

Outputs OUT(1...n) leakage current

HS leakage current in off state	I _{QLHn_NOR}	-2	-0.5	-	μA	<i>V</i> _{OUTn} = 0V; EN=High P_4.4.32
HS leakage current in off state	I _{QLHn_SLE}	-2	-0.5	-	μA	<i>V</i> _{OUTn} = 0V; EN=GND P_4.4.33
LS Leakage current in off state	I _{QLLn_NOR}	-	0.5	2	μA	$V_{OUTn} = V_S$; EN=High P_4.4.34
LS Leakage current in off state	I _{QLLn_SLE}	-	0.5	2	μA	$V_{\rm OUTn} = V_{\rm S}$; EN=GND P_4.4.35

Output Switching Times. See Figure 9 and Figure 10.

Slew rate of high-side and low-	d _{vout} / dt	0.1	0.45	0.75	V/µs	Resistive load =	P_4.4.36
side outputs						100Ω; $V_{\rm S}$ =13.5V ⁴⁾	



Table 5Electrical Characteristics, $V_s = 5.5 V$ to 18 V, $V_{DD} = 3.0V$ to 5.5V, $T_j = -40^{\circ}$ C to $+150^{\circ}$ C, EN= HIGH,
 $I_{OUTn} = 0$ A; Typical values refer to $V_{DD} = 5.0 V$, $V_s = 13.5 V$ and $T_J = 25^{\circ}$ C unless otherwise
specified; all voltages with respect to ground, positive current flowing into pin (unless
otherwise specified) (cont'd)

Parameter	Symbol		Value	5	Unit	Note or	Number	
		Min.	Тур.	Max.	1	Test Condition		
Output delay time high side driver on	t _{dONH}	5	20	35	μs	Resistive load = 100Ω to GND	P_4.4.37	
Output delay time high side driver off	t _{dOFFH}	15	45	75	μs	Resistive load = 100Ω to GND	P_4.4.38	
Output delay time low side driver on	t _{dONL}	5	20	35	μs	Resistive load = 100Ω to VS	P_4.4.39	
Output delay time low side driver off	t _{dOFFL}	15	45	75	μs	Resistive load = 100Ω to VS	P_4.4.40	
Cross current protection time, high to low	t _{DHL}	100	130	160	μs	Resistive load = $100\Omega^{3}$	P_4.4.41	
Cross current protection time, low to high	t _{DLH}	100	130	160	μs	Resistive load = $100\Omega^{3}$	P_4.4.42	
Input Interface: Logic Input El	N			4		-		
High-input voltage	V _{ENH}	0.7 * V _{DD}	-	-	V	-	P_4.4.43	
Low-input voltage	V _{ENL}	-	-	0.3 * V _{DD}	V	-	P_4.4.44	
Hysteresis of input voltage	V _{ENHY}	-	500	-	mV	3)	P_4.4.45	
Pull down resistor	R _{PD_EN}	20	40	70	kΩ	$V_{\rm EN} = 0.2 \times V_{\rm DD}$	P_4.4.46	
SPI frequency								
Maximum SPI frequency	f _{SPI,max}	_	-	5.0	MHz	3) 5)	P_4.4.47	
SPI INTERFACE: Delay Time fro		g edge to	first D	ata in				
Setup time	t _{set}	-	-	150	μs	³⁾ See Figure 14	P_4.4.48	
SPI INTERFACE: Input Interfac	e, Logic Inp	uts SDI,	SCLK, O	CSN				
H-input voltage threshold	V _{IH}	0.7 * V _{DD}	-	-	V	-	P_4.4.50	
L-input voltage threshold	V _{IL}	-	-	0.3 * V _{DD}	V	-	P_4.4.51	
Hysteresis of input voltage	V _{IHY}	-	500	-	mV	3)	P_4.4.52	
Pull up resistor at pin CSN	R _{PU_CSN}	30	50	80	kΩ	$V_{\rm CSN} = 0.7 \times V_{\rm DD}$	P_4.4.53	
Pull down resistor at pin SDI, SCLK	R _{PD_SDI,} R _{PD_SCLK}	20	40	70	kΩ	$V_{\rm SDI}, V_{\rm SCLK} = 0.2 \text{ x} V_{\rm DD}$	P_4.4.54	
Input capacitance at pin CSN, SDI or SCLK	C	-	10	15	pF	0V < V _{DD} < 5.25V ³⁾	P_4.4.55	
Input Interface, Logic Output	SDO							
H-output voltage level	V _{SDOH}	V _{DD} - 0.4	V _{DD} - 0.2	-	V	I _{SDOH} = -1.6 mA	P_4.4.56	



Table 5Electrical Characteristics, $V_s = 5.5 V$ to 18 V, $V_{DD} = 3.0V$ to 5.5V, $T_j = -40^{\circ}$ C to $+150^{\circ}$ C, EN= HIGH,
 $I_{OUTn} = 0 A$; Typical values refer to $V_{DD} = 5.0 V$, $V_s = 13.5 V$ and $T_J = 25^{\circ}$ C unless otherwise
specified; all voltages with respect to ground, positive current flowing into pin (unless
otherwise specified) (cont'd)

Parameter	Symbol		Value	s	Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
L-output voltage level	V _{SDOL}	_	0.2	0.4	V	/ _{SDOL} = 1.6 mA	P_4.4.57
Tri-state Leakage Current	I _{SDOLK}	-1	-	1	μΑ	$V_{\rm CSN} = V_{\rm DD};$ $0V < V_{\rm SDO} < V_{\rm DD}$	P_4.4.58
Tri-state input capacitance	C _{SDO}	-	10	15	рF	3)	P_4.4.59
Data Input Timing. See Figure	15 and Figu	ire 17.					
SCLK Period	t _{pCLK}	200	-	-	ns	3)	P_4.4.60
SCLK High Time	t _{sclkh}	0.45 * t _{рСLK}	-	0.55 * t _{pCLK}	ns	3)	P_4.4.61
SCLK Low Time	t _{sclkl}	0.45 * t _{pCLK}	-	0.55 * t _{pCLK}	ns	3)	P_4.4.62
SCLK Low before CSN Low	t _{BEF}	125	-	_	ns	3)	P_4.4.63
CSN Setup Time	t _{lead}	250	-	-	ns	3)	P_4.4.64
SCLK Setup Time	t _{lag}	250	-	-	ns	3)	P_4.4.65
SCLK Low after CSN High	t _{BEH}	125	-	-	ns	3)	P_4.4.66
SDI Setup Time	t _{SDI_setup}	30	-	-	ns	3)	P_4.4.67
SDI Hold Time	t _{SDI_hold}	30	-	-	ns	3)	P_4.4.68
Input Signal Rise Time at pin SDI, SCLK, CSN	t _{rIN}	-	-	50	ns	3)	P_4.4.69
Input Signal Fall Time at pin SDI, SCLK, CSN	t _{fIN}	-	-	50	ns	3)	P_4.4.70
Delay time from EN falling edge to standby mode	t _{dmode}	-	-	8	μs	3)	P_4.4.71
Minimum CSN High Time	t _{csnh}	5	-	-	μs	3)	P_4.4.72
Data Output Timing. See Figur	e 15.		ł		1		
SDO Rise Time	t _{rSDO}	-	30	80	ns	$C_{load} = 40 p F^{3}$	P_4.4.73
SDO Fall Time	t _{fSDO}	-	30	80	ns	$C_{load} = 40 p F^{3}$	P_4.4.74
SDO Enable Time after CSN falling edge	t _{ensdo}	-	-	75	ns	Low Impedance ³⁾	P_4.4.75
SDO Disable Time after CSN rising edge	t _{DISSDO}	-	-	75	ns	High Impedance ³⁾	P_4.4.76
Duty cycle of incoming clock at SCLK	duty _{SCLK}	45	-	55	%	3)	P_4.4.77
SDO Valid Time for V _{DD} = 3.3V	t _{VASDO3}	-	70	95	ns	$V_{SDO} < 0.2 \times V_{DD}$ $V_{SDO} > 0.8 \times V_{DD}$ $C_{load} = 40 \text{pF}^{-3}$	P_4.4.78



Table 5Electrical Characteristics, $V_s = 5.5 V$ to 18 V, $V_{DD} = 3.0V$ to 5.5V, $T_j = -40^{\circ}$ C to $+150^{\circ}$ C, EN= HIGH,
 $I_{OUTn} = 0 A$; Typical values refer to $V_{DD} = 5.0 V$, $V_s = 13.5 V$ and $T_J = 25^{\circ}$ C unless otherwise
specified; all voltages with respect to ground, positive current flowing into pin (unless
otherwise specified) (cont'd)

Parameter	Symbol		Values			Note or	Number
		Min.	Тур.	Max.		Test Condition	
SDO Valid Time for <i>V</i> _{DD} = 5V	t _{vasdo5}	-	50	65	ns	$V_{SDO} < 0.2 \times V_{DD}$ $V_{SDO} > 0.8 V_{DD}$ $C_{load} = 40 pF^{3}$	P_4.4.79

Thermal warning & Shutdown

Thermal warning junction temperature	T _{jW}	120	140	170	°C	See Figure 11 ³⁾	P_4.4.80
Thermal shutdown junction temperature	T _{jSD}	150	175	200	°C	See Figure 11 ³⁾	P_4.4.81
Thermal comparator hysteresis	T _{jHYS}	-	5	-	°C	3)	P_4.4.82
Ratio of SD to W temperature	$T_{\rm jSD}/T_{\rm jW}$	1.05	1.20	-	-	3)	P_4.4.83

1) $I_{\rm S HSON}$ does not include the load current

2) HS1, respectively HS2, is set to LED mode by setting OL_SEL_HS1 bit to 1, respectively OL_SEL_HS2 bit to 1

3) Not subject to production test, specified by design

4) Measured for 20% - 80% of $V_{\rm S}$.

5) Not applicable in daisy chain configuration

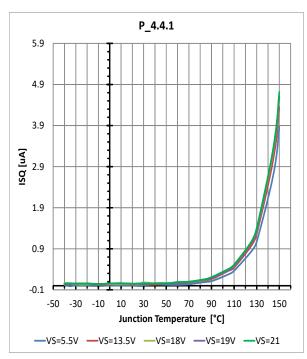


4 Characterization results

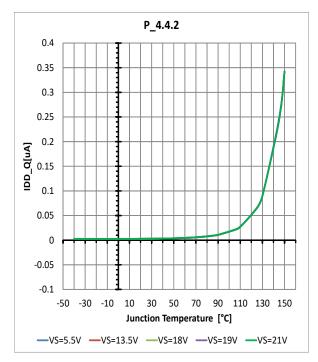
Performed on 7 devices from 2 lots, over operating temperature and nominal/extended supply range.

Typical performance characteristics

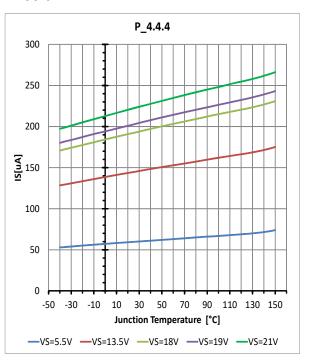
Supply quiescent current



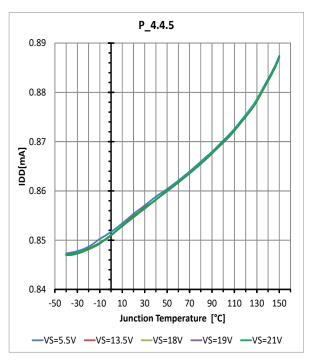
Logic supply quiescent current



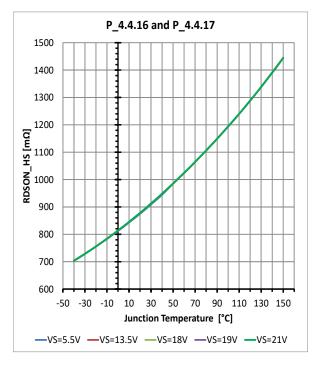
Supply current



Logic supply current

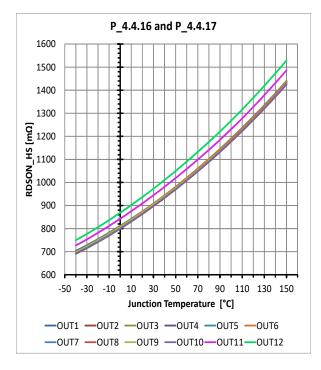






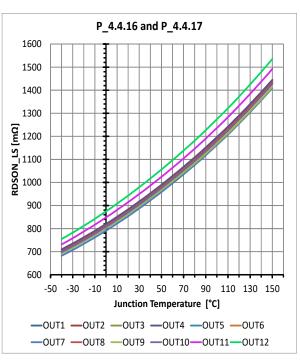
HS static Drain-source ON-resistance

HS static drain-source ON-resistance VS = 13.5V and VDD = 5V



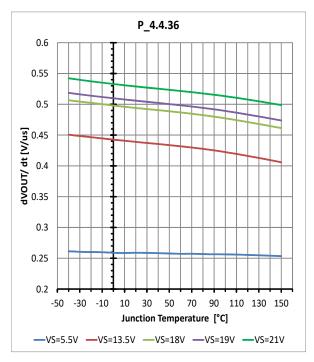
P_4.4.16 and P_4.4.17

LS static drain-source ON-resistance VS = 13.5V and VDD = 5V



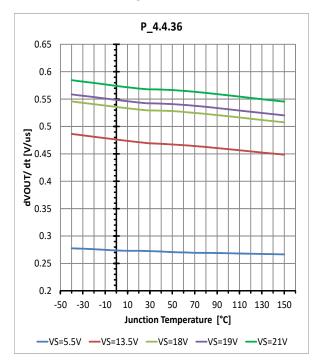
LS static Drain-source ON-resistance



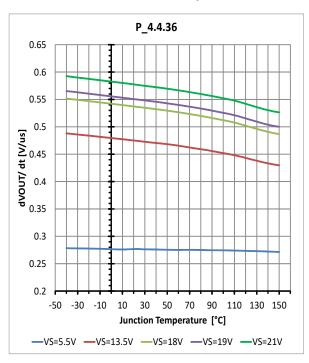


Slew rate ON of high-side outputs

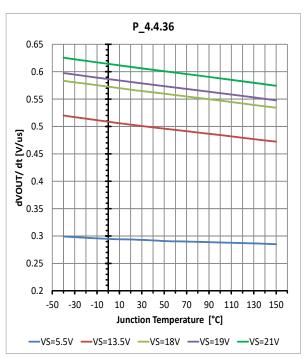
Slew rate OFF of high-side outputs



Slew rate ON of low-side outputs

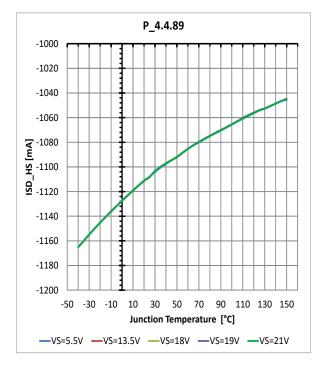


Slew rate OFF of low-side outputs



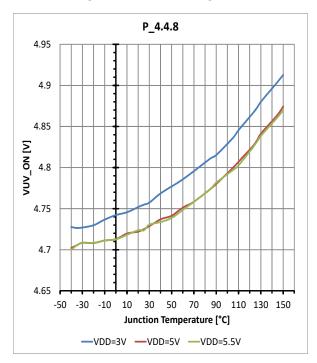


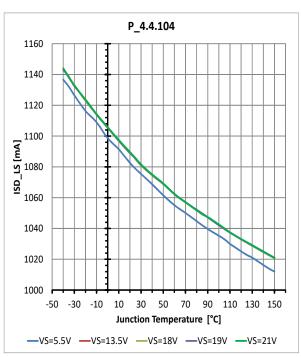




HS overcurrent shutdown threshold

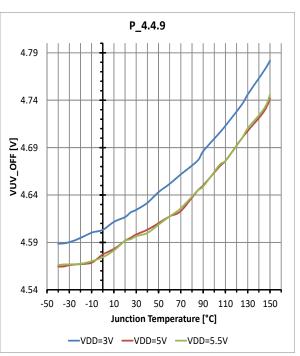
Undervoltage switch ON voltage threshold



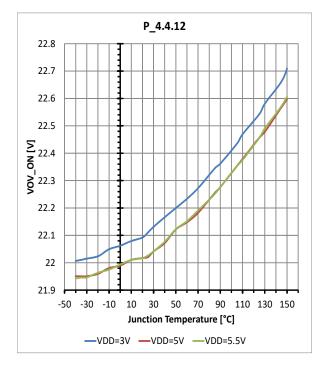


LS overcurrent shutdown threshold

Undervoltage switch OFF voltage threshold

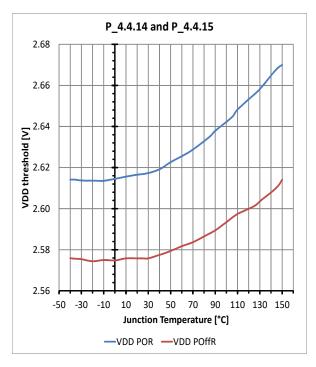




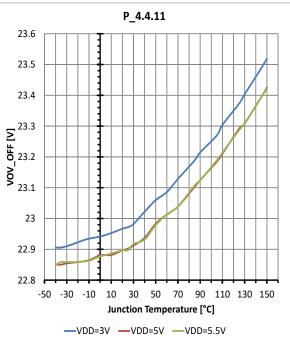


Overvoltage switch ON voltage threshold

VDD Power-on-reset and VDD Power-off-reset









General Description

5 General Description

5.1 Power Supply

The TLE94112ES has two power supply inputs, $V_{\rm S}$ and $V_{\rm DD}$. The half bridge outputs are supplied by $V_{\rm S}$, which is connected to the 12V automotive supply rail. $V_{\rm DD}$ is used to supply the I/O buffers and internal voltage regulator of the device.

 $V_{\rm S}$ and $V_{\rm DD}$ supplies are separated so that information stored in the logic block remains intact in the event of voltage drop outs or disturbances on $V_{\rm S}$. The system can therefore continue to operate once $V_{\rm S}$ has recovered, without having to resend commands to the device.

A rising edge on V_{DD} crossing $V_{DD POR}$ triggers an internal Power-On Reset (POR) to initialize the IC at power-on. All data stored internally is deleted, and the outputs are switched off (high impedance).

An electrolytic and 100nF ceramic capacitors are recommended to be placed as close as possible to the $V_{\rm S}$ supply pin of the device for improved EMC performance in the high and low frequency band. The electrolytic capacitor must be dimensioned to prevent the VS voltage from exceeding the absolute maximum rating. In addition, decoupling capacitors are recommended on the $V_{\rm DD}$ supply pin.

5.2 Operation modes

5.2.1 Normal mode

The TLE94112ES enters normal mode by setting the EN input High. In normal mode, the charge pump is active and all output transistors can be configured via SPI.

5.2.2 Sleep mode

The TLE94112ES enters sleep mode by setting the EN input Low. The EN input has an internal pull-down resistor.

In sleep mode, all output transistors are turned off and the SPI register banks are reset. The current consumption is reduced to $I_{SQ} + I_{DD_Q}$.

5.3 Reset Behaviour

The following reset triggers have been implemented in the TLE94112ES:

V_{DD} Undervoltage Reset:

The SPI Interface shall not function if V_{DD} is below the undervoltage threshold, $V_{DD POffR}$. The digital block will be deactivated, the logic contents cleared and the output stages are switched off. The digital block is initialized once V_{DD} voltage levels is above the undervoltage threshold, $V_{DD POR}$. Then the NPOR bit is reset (NPOR = 0 in **SYS_DIAG1** and Global Status Register).

Reset on EN pin:

If the EN pin is pulled Low, the logic content is reset and the device enters sleep mode.

The reset event is reported by the NPOR bit (NPOR = 0) once the TLE94112ES is in normal mode (EN = High; VDD > $V_{DD POR}$).



General Description

5.4 Reverse Polarity Protection

The TLE94112ES requires an external reverse polarity protection. During reverse polarity, the free-wheeling diodes across the half bridge output will begin to conduct, causing an undesired current flow (I_{RB}) from ground potential to battery and excessive power dissipation across the diodes. As such, a reverse polarity protection diode is recommended (see **Figure 4**).

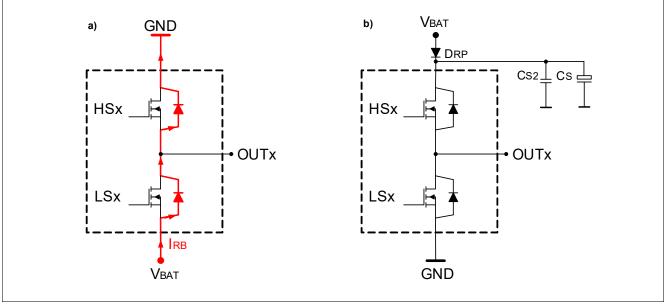


Figure 4 Reverse Polarity Protection



6 Half-Bridge Outputs

6.1 Functional Description

The half-bridge outputs of the TLE94112ES are intended to drive motor loads. These outputs can either be driven continuously or PWM enabled via SPI.

If the outputs are driven continuously via SPI, for example HS1 and LS2 used to drive a motor, then the following suggested SPI commands shall be sent:

- Activate HS1: Bit HB1_HS_EN in HB_ACT_1_CTRL register
- Activate LS2: Bit HB2_LS_EN in HB_ACT_1_CTRL register

6.1.1 Half-bridge operation with PWM enabled

All half-bridge outputs of the TLE94112ES are capable of PWM operation. They can either be used to drive an inductive load (e.g. DC brush motor) or optionally a resistive load (e.g. LED). Each half-bridge output has been allocated a maximum of three PWM channels with individual duty cycle settings with 8-bit resolution. Each channel is further mapped to a maximum of three PWM frequency options, i.e. 80Hz,100Hz and 200Hz. This feature enables a highly flexible PWM operation while driving loads with varying control profiles.

PWM frequency and duty cycle can be changed on demand during PWM operation of the desired half-bridge output. Glitches on the PWM output waveform, which may arise as a result of on-demand changes in PWM operation, will be prevented by the internal logic circuitry.

When operating with motor loads, active or passive free-wheeling configuration is available via SPI to select the speed at which the inductive current can decay over the full-bridge circuit. The default setting is passive free-wheeling.

Note: Active free-wheeling is effectively applied if the selected duty cycle corresponds to turn-on times of the HS and the LS, which are longer than the sum of the cross conduction times tDHL + tDLH.

Control Register: HBx_MODEn (n=0,1)	PWM Frequency 80Hz (Control Register: PWM_CH_FREQ_CTRL)	PWM Frequency 100Hz (Control Register: PWM_CH_FREQ_CTRL)	PWM Frequency 200Hz (Control Register: PWM_CH_FREQ_CTRL)
PWM Channel 1	PWM_CH1_FREQ_n (n=0,1)	PWM_CH1_FREQ_n (n=0,1)	PWM_CH1_FREQ_n (n=0,1)
	Bit '01 _B '	Bit '10 _B '	Bit '11 _B '
PWM Channel 2	PWM_CH2_FREQ_n (n=0,1)	PWM_CH2_FREQ_n (n=0,1)	PWM_CH2_FREQ_n (n=0,1)
	Bit '01 _B '	Bit '10 _B '	Bit '11 _B '
PWM Channel 3	PWM_CH3_FREQ_n (n=0,1)	PWM_CH3_FREQ_n (n=0,1)	PWM_CH3_FREQ_n (n=0,1)
	Bit '01 _B '	Bit '10 _B '	Bit '11 _B '

Table 6	PWM capability and frequency selection per half-bridge output



6.1.1.1 Inductive Load

An illustration is shown in **Figure 5** with OUT1 and OUT2 driving a DC brush motor. With this configuration, HS1 is permanently driven while LS2 is driven in PWM operation. HS2 serves to actively free-wheel (FW) the motor current load, reducing the power dissipation of the device.

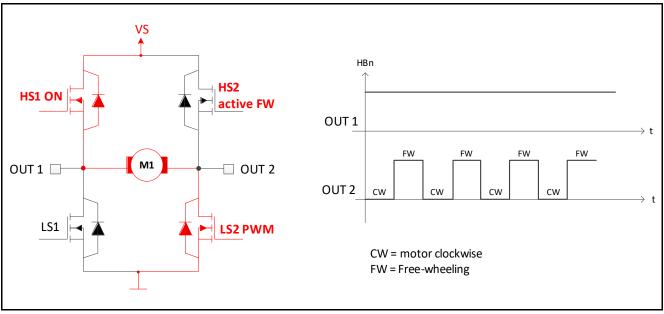


Figure 5 PWM operation on OUT 2

Assuming HBx Mode = 00 and both HSx and LSx are considered off (tri-state). The suggested SPI control commands for proper PWM operation are:

Option 1: The considered output is not put in parallel with another one

- Configure the frequency to 00 (PWM is stopped and off) for selected PWM channel
- Configure active or passive free-wheeling of the inductive decay current in FW_CTRL register
- Assign an appropriate PWM channel for selected half-bridge output in HB_MODE_CTRL register
- Configure the duty cycle of the selected half-bridge output in PWM_DC_CTRL register
- Select the PWM frequency in PWM_CH_FREQ_CTRL register to begin the PWM period
- Activate the channel to be driven in PWM operation: HSn or LSn in the HB_ACT_CTRL register

Option 2: Outputs controlled by different control registers are put paralleled. This sequence ensures that corresponding HS or LS are activated simultaneously

- Configure the frequency 00 (PWM is stopped and off) for selected PWM channel
- Configure active or passive free-wheeling of the inductive decay current in FW_CTRL register
- Assign an appropriate PWM channel for selected half-bridge output in HB_MODE_CTRL register
- Configure the duty cycle of the selected half-bridge output in PWM_DC_CTRL register
- Activate the channel to be driven in PWM operation: HSn or LSn in the HB_ACT_CTRL register
- Select the PWM frequency in PWM_CH_FREQ_CTRL register to begin the PWM period

Careful attention should be paid to the free-wheeling configuration of the half-bridge required to be driven in PWM operation. For example, in the event a high-side channel is activated and assigned a PWM channel, and active free-wheeling is selected, but a frequency mode of '00' (PWM is stopped and off) is configured in the



PWM_CH_FREQ_CTRL register, then the respective high-side channel will be configured low and the adjacent low-side channel within the half-bridge will be enabled. This is a result of enabling active free-wheeling.



6.1.1.2 LED mode (optional)

Outputs, OUT1 and OUT2, are designed to optionally drive low current loads such as LEDs. The high-side channels, HS1 and HS2 are equipped with a lower open load threshold detection current and shorter filter time, specifically for low current loads such as LEDs. See OL_SEL_HS1 and OL_SEL_HS2 bits in FW_OL_CTRL register. Setting HS1 or HS2 in LED mode increases the R_{DSON} and decreases the open load detection threshold. An illustration is shown in **Figure 6** with OUT1 driving an LED. With this configuration, HS1 is driven in PWM operation while LS1 is deactivated.

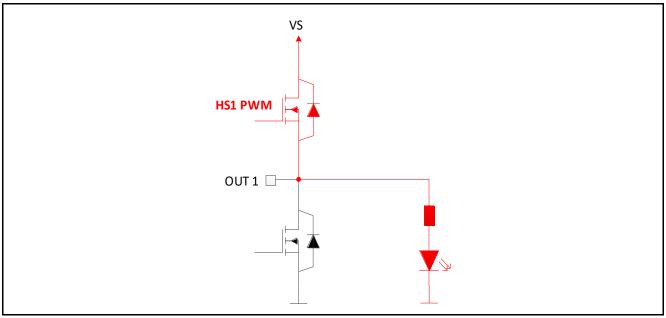


Figure 6 PWM operation on OUT 1

Assuming HBx Mode = 00 and both HSx and LSx are considered off (tri-state). The suggested SPI control commands are:

- Configure frequency 00 (PWM is stopped and off) for selected channel to ensure PWM is off.
- Assign an appropriate PWM channel for selected HS1 or HS2 output in HB_MODE_CTRL register
- Configure duty cycle of selected HS1 or HS2 output in PWM_DC_CTRL register
- Activate channel to be driven in PWM operation: HS1 or HS2 in the HB_ACT_CTRL register
- Select low current open load detection threshold for HS1 or HS2 in FW_OL_CTRL register
- Select PWM frequency in PWM_CH_FREQ_CTRL register to begin the PWM period.



6.2 Protection & Diagnosis

The TLE94112ES is equipped with an SPI interface to control and diagnose the state of the half-bridge drivers. This device has embedded protective functions which are designed to prevent IC destruction under fault conditions described in the following sections. Fault conditions are treated as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

The following table provides a summary of fault conditions, protection mechanisms and recovery states embedded in the TLE94112ES device.

Fault condition	Error Flag (EF) behaviour	Error bit: Status Register	Output Protection mechanism	Output error state	Output and error flag (EF) recovery
Overcurrent	Latch	 Load Error bit, LE (bit 6) in SYS_DIAG 1: Global Status 1 Register Localized error for each HS and LS channel of half-bridge, HBn_HS_OC and HBn_LS_OC bits in SYS_DIAG_2, SYS_DIAG_3, SYS_DIAG_4 status registers. 	Error output shutdown and latched	High-Z	Half-bridge control bits remain set despite error, however the output stage is shutdown. Clear EF to reactivate output stage.
Open load	Latch	 Load Error bit, LE (bit 6) in SYS_DIAG 1: Global Status 1 Register Localized error for each HS and LS channel of half-bridge, HBn_HS_OL and HBn_LS_OL bits in SYS_DIAG_5, SYS_DIAG_6, SYS_DIAG_7 status registers. 	None	No state change	An open load detection does not change the state of the output. EF to be cleared.
Temperature pre-warning	Latch	Global error bit 1, TPW in SYS_DIAG_1: Global Status 1 register	None	No state change	Not applicable
Temperature shutdown	Latch	Global error bit 2, TSD in SYS_DIAG_1: Global Status 1 register	All outputs shutdown and latched.	High-Z	Half-bridge control bits remain set despite error, however the output stage is shutdown. Clear EF to reactivate output stage.

Table 7Summary of diagnosis and monitoring of outputs



Fault condition	Error Flag (EF) behaviour	Error bit: Status Register	Output Protection mechanism	Output error state	Output and error flag (EF) recovery
Powersupply failure due to undervoltage	Latch	Global error bit 5, VS_UV in SYS_DIAG_1: Global Status 1 register	All outputs shutdown and automatically recovers.	High-Z	Half-bridge control bits remain set despite error, however the output stage is shutdown. They will automatically be reactivated once the power supply recovers. EF to be cleared.
Powersupply failure due to overvoltage	Latch	Global error bit 4, VS_OV in SYS_DIAG_1: Global Status 1 register	All outputs shutdown and automatically recover.	High-Z	Half-bridge control bits remain set despite error, however the output stage is shutdown. They will automatically be reactivated once the power supply recovers. EF to be cleared.

Table 7 Summary of diagnosis and monitoring of outputs (cont'd)



6.2.1 Short Circuit of Output to Supply or Ground

The high-side switches are protected against short to ground whereas the low-side switches are protected against short to supply.

The high-side and low-side power switches will enter into an over-current condition if the current within the switch exceeds the overcurrent shutdown detection threshold, I_{SD} . Upon detection of the I_{SD} threshold, an overcurrent shutdown filter, t_{dSD} is begun. As the current rises beyond the threshold I_{SD} , it will be limited by the current limit threshold, I_{LIM} . Upon expiry of the overcurrent shutdown filter time, the affected power switch is latched off and the corresponding error bit, HBn_HS_OC or HBn_LS_OC is set and latched. See **Figure 7** and **Figure 8** for more detail. A global load error bit, LE, contained in the global status register, SYS_DIAG_1, is also set for ease of error scanning by the application software. The power switch remains deactivated as long as the error bit is set.

To resume normal functionality of the power switch (in the event the overcurrent condition disappears or to verify if the failure still exists) the microcontroller shall clear the error bit in the respective status register to reactivate the desired power switch.

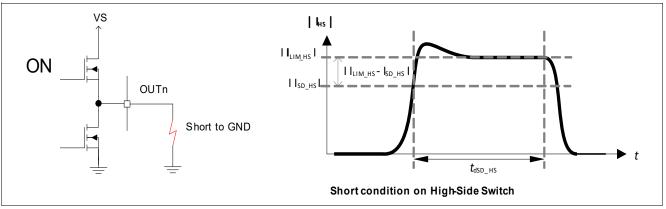
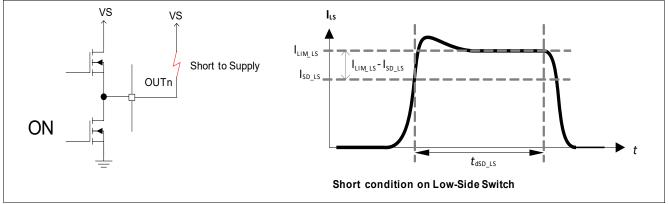


Figure 7 High-Side Switch - Short Circuit and Overcurrent Protection







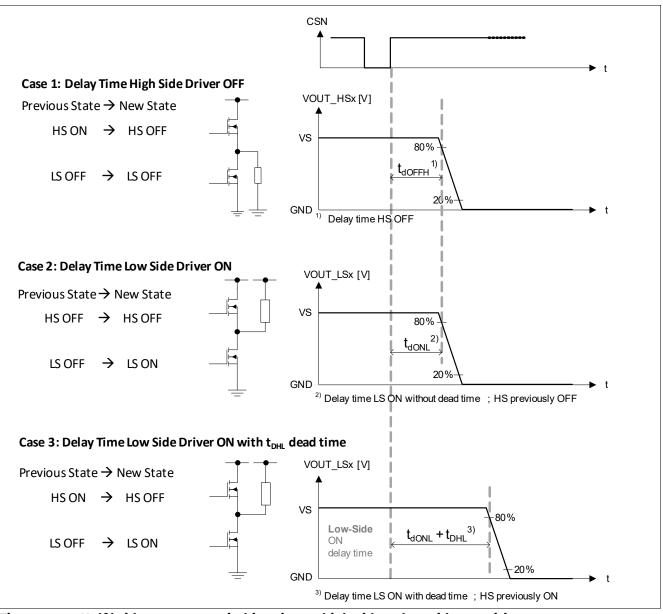
a	ctivated power swit	ch				
REGISTER	REGISTER NAME	Bit	BEFORE OVERCURRENT	DURING OVERCURRENT	AFTER OVERCURRENT Bit State	
ΤΥΡΕ			Bit State	Bit State		
Control	HB_ACT_CTRL_n	HBn_HS_EN HBn_LS_EN	1	1	1 (corresponding half-bridge deactivated)	
Status	SYS_DIAG_1: Global Status 1	LE	0	0	1	
Status	SYS_DIAG_x where x=2,3,4	HBn_HS_OC HBn_LS_OC	0	0	1	

Table 8Control and Status register bit state in the event of an overcurrent condition for an
activated power switch



6.2.2 Cross-Current

In bridge configurations the high-side and low-side power transistors are ensured never to be simultaneously "ON" to avoid cross currents. This is achieved by integrating delays in the driver stage of the power outputs to create a dead-time between switching off of one power transistor and switching on of the adjacent power transistor within the half-bridge. The dead times, t_{DHL} and t_{DLH} , as shown in **Figure 9** case 3 and **Figure 10** case 3, have been specified to ensure that the switching slopes do not overlap with each other. This prevents a cross conduction event.







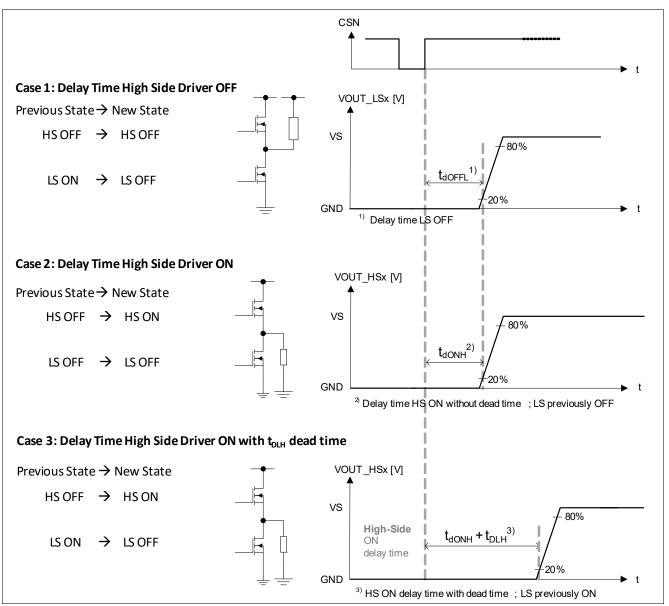


Figure 10 Half bridge outputs switching times- low-side to high-side transition



6.2.3 Temperature Monitoring

Temperature sensors are integrated in the power stages. The temperature monitoring circuit compares the measured temperature to the warning and shutdown thresholds. If one or more temperature sensors reach the warning temperature, the temperature pre-warning bit, TPW is set. This bit is latched and can only be cleared via SPI. The outputs stages however remain activated.

If one or more temperature sensors reach the shut-down temperature threshold, **all outputs are latched off**. The TSD bit in SYS_DIAG_1: Global Status 1 is set. All outputs remain deactivated until the TSD bit is cleared. See **Figure 11**.

To resume normal functionality of the power switch (in the event the overtemperature condition disappears, or to verify if the failure still exists) the microcontroller shall clear the TSD error bit in the status register to reactivate the respective power switch.

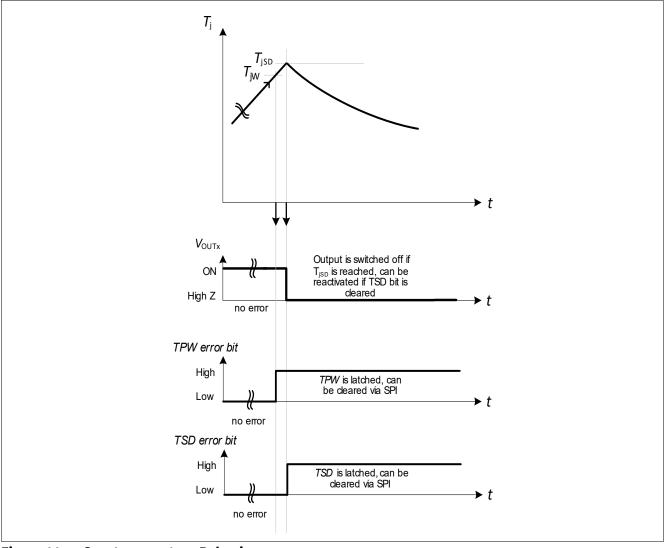


Figure 11 Overtemperature Behavior



	activated power switch									
			$T_{\rm j} < T_{\rm jW}$	$T_{j} > T_{jW}$	$T_j > T_{jSD}$	$T_j < T_{jSD} - T_{jHYS}$				
REGISTER TYPE	REGISTER NAME	Bit	Bit State	Bit State	Bit State	Bit State				
Control	HB_ACT_CTRL_n	HBn_HS_EN HBn_LS_EN	1	1	1 (all outputs are latched off)	'1' (outputs are latched off unless error is cleared)				
Status	SYS_DIAG_1: Global status 1	TPW	0	1 (latched)	1 (latched)	'0' if error is cleared and T _j < T _{jW} , else '1'				
Status	SYS_DIAG_1: Global status 1	TSD	0	0	1 (latched)	'0' if error is cleared, else '1'				

Table 9Control and Status register bit state in the event of an overtemperature condition for an
activated power switch

6.2.4 Overvoltage and undervoltage shutdown

The power supply rails $V_{\rm S}$ and $V_{\rm DD}$ are monitored for supply fluctuations. The $V_{\rm S}$ supply is monitored for underand over-voltage conditions where as the $V_{\rm DD}$ supply is monitored for under-voltage conditions.

6.2.4.1 V_s Undervoltage

In the event the supply voltage V_S drops below the switch off voltage V_{UVOFF} , all output stages are switched off, however, the logic information remains intact and uncorrupted. The V_S under-voltage error bit, VS_UV, located in SYS_DIAG_1: Global Status 1 status register, will be set and latched. If V_S rises again and reaches the switch on voltage V_{UVON} threshold, the power stages will automatically be activated. The VS_UV error bit should be cleared to verify if the supply disruption is still present. See **Figure 12**.

6.2.4.2 V_s Overvoltage

In the event the supply voltage V_S rises above the switch off voltage $V_{OV OFF}$, all output stages are switched off. The V_S over-voltage error bit, VS_OV, located in SYS_DIAG_1: Global Status 1 status register, will be set and latched. If V_S falls again and reaches the switch on voltage $V_{OV ON}$ threshold, the power stages will automatically be activated. The VS_OV error bit should be cleared to verify if the overvoltage condition is still present. See **Figure 12**.

6.2.4.3 V_{DD} Undervoltage

In the event the VDD logic supply decreases below the undervoltage threshold, V_{DD POffR}, the SPI interface shall no longer be functional and the TLE94112ES will enter reset.

The digital block will be initialized and the output stages are switched off to High impedance. The undervoltage reset is released once V_{DD} voltage levels are above the undervoltage threshold, $V_{DD POR}$.

The reset event is reported in SYS_DIAG1 by the NPOR bit (NPOR = 0) once the TLE94112ES is in normal mode (EN = High; VDD > $V_{DD POR}$).

TLE94112ES



Half-Bridge Outputs

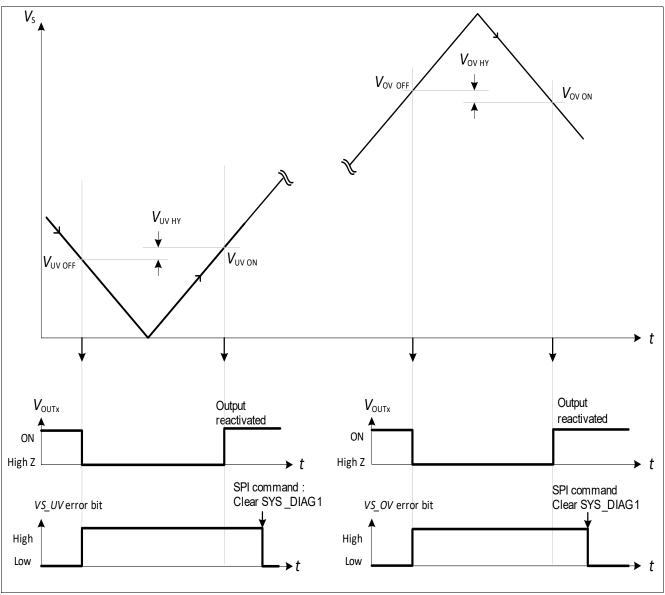


Figure 12 Output behavior during under- and overvoltage V_s condition

6.2.5 Open Load

Both high-side and low-side switches of the half-bridge power outputs are capable of detecting an open load in their activated state. If a load current lower than the open load detection threshold, I_{OLD} for at least t_{dOLD} is detected at the activated switch, the corresponding error bit, HBn_HS_OL or HBn_LS_OL is set and latched. A global load error bit, LE, in the global status register, SYS_DIAG_1: Global Status 1, is also set for ease of error scanning by the application software. The half-bridge output however, remains activated.

The microcontroller must clear the error bit in the respective status register to determine if the open load is still present or disappeared.

High-side outputs, HS1 and HS2, are specifically designed to detect open load thresholds for LED loads. Both HS1 and HS2 have a unique and lower open load current threshold and filter time which are configurable via SPI in control register, FW_OL_CTRL.

During PWM operation, the open load detection is blanked and will not be visible in the status register for power stages used in active free-wheeling



7 Serial Peripheral Interface (SPI)

The TLE94112ES has a 16-bit SPI interface for output control and diagnostics. This section describes the SPI protocol, the control and status registers.

7.1 SPI Description

The 16-bit wide Control Input Word is read via the data input SDI, which is synchronized with the clock input SCLK provided by the microcontroller. SCLK must be Low during CSN falling edge (Clock Polarity = 0). The SPI incorporates an in-frame response: the content of the addressed register is shifted out at SDO within the same SPI frame (see **Figure 19** and **Figure 21**). The transmission cycle begins when the chip is selected by the input CSN (Chip Select Not), Low active. After the CSN input returns from Low to High, the word that has been read is interpreted according to the content. The SDO output switches to tri-state status (High impedance) at this point, thereby releasing the SDO bus for other use. The state of SDI is shifted into the input register with every falling edge on SCLK. The state of SDO is shifted out of the output register at every rising edge on SCLK (Clock Phase = 1). The SPI protocol of the TLE94112ES is compatible with independent slave configuration and with daisy chain. Daisy chaining is applicable to SPI devices with the same protocol.

Writing, clearing and reading is done byte wise. The SPI configuration and status bits are not cleared automatically by the device and therefore must be cleared by the microcontroller, e.g. if the TSD bit was set due to over temperature (refer to the respective register description for detailed information).

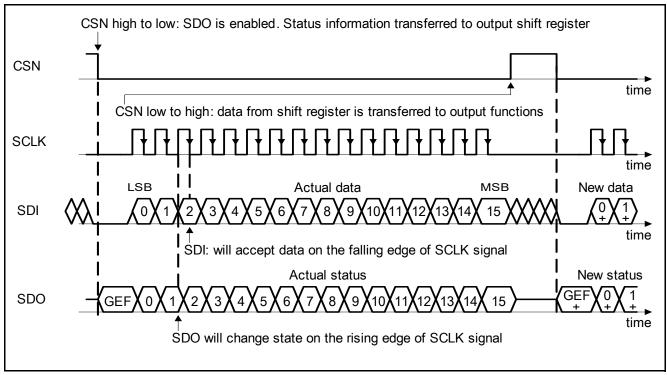


Figure 13 SPI Data Transfer Timing (note the reversed order of LSB and MSB as shown in this figure compared to the register description)

SPI messages are only recognized if a minimum set time, tSET, is observed upon rising edge of the EN pin (Figure 14).



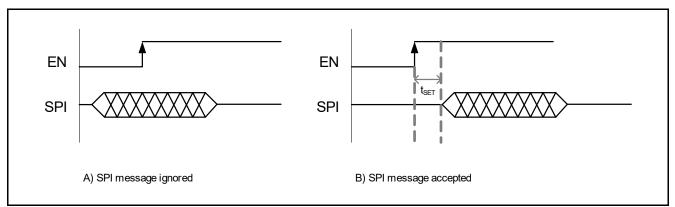


Figure 14 Setup time from EN rising edge to first SPI communication

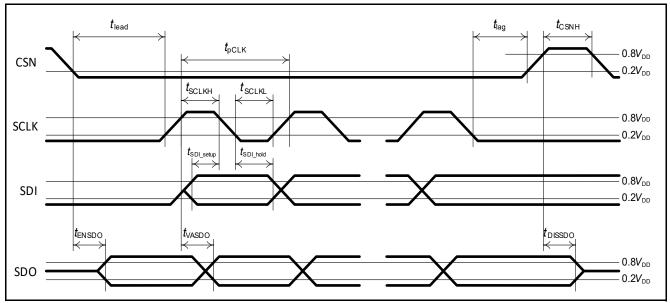


Figure 15 SPI Data Timing

7.1.1 Global Error Flag

A logic OR combination between Global Error Flag (GEF) and the signal present on SDI is reported on SDO between a CSN falling edge and the first SCLK rising edge (**Figure 13**). GEF is set if a fault condition is detected or if the device comes from a Power On Reset (POR).

Note: The SDI pin of all devices in daisy chain or non daisy chain mode must be Low at the beginning of the SPI frame (between the CSN falling edge and the first SCLK rising edge).

It is possible to check if the TLE94112ES has detected a fault by reading the GEF without SPI clock pulse (**Figure 16**).



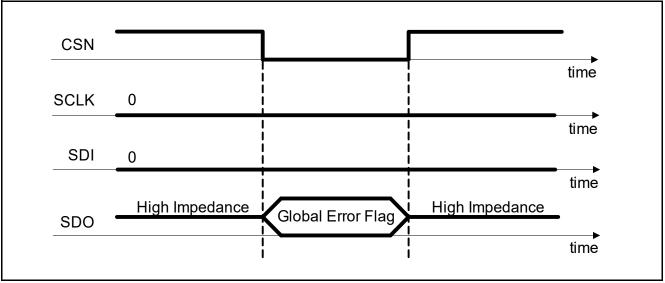


Figure 16 SDO behaviour with 0-clock cycle

7.1.2 Global Status Register

The SDO shifts out during the first eight SCLK cycles the Global Status Register. This register provides an overview of the device status. All failures conditions are reported in this byte:

- SPI protocol error (SPI_ERR)
- Load Error (LE bit): logical OR between Open Load (OL) and Overcurrent (OC) failures
- VS Undervoltage (VS_UV bit)
- VS Overvoltage (VS_OV bit)
- Negated Power ON Reset (NPOR bit)
- Temperature Shutdown (TSD bit)
- Temperature Pre-Warning (TPW bit)

See **Chapter 7.7.1** for details.

The following table shows how failures are reported in the Global Status Register and by the Global Error Flag.

•	6	6
Type of Error	Failure reported in the Global Status Register	Global Error Flag
SPI protocol error	SPI_ERR = 1	1
Open load or Overcurrent	LE = 1	1
VS Undervoltage	VS_UV = 1	1
VS Overvoltage	VS_OV = 1	1
Power ON Reset	NPOR = 0	1
Thermal Shutdown	TSD = 1	1

Table 10 Fa	ailure reported in the	Global Status R	Register and Global Error Flag	
-------------	------------------------	------------------------	--------------------------------	--

Note: The Global Error Flag is a logic OR combination of every bit of the Global Status Register with the exception of NPOR: GEF = (SPI_ERR) OR (LE) OR (VS_UV) OR (VS_OV) OR (NOT(NPOR)) OR (TSD) OR (TPW).



Type of Error	Failure reported in the Global Status Register	Global Error Flag
Thermal Warning	TPW = 1	1
No Error and no Power ON Reset	SPI_ERR = 0 LE = 0 VS_UV = 0 VS_OV = 0	0
	NPOR = 1 TSD = 0 TPW = 0	

Table 10Failure reported in the Global Status Register and Global Error Flag

Note: The default value (after Power ON Reset) of NPOR is 0, therefore the default value of GEF is 1.

7.1.3 SPI protocol error detection

The SPI incorporates an error flag in the Global Status Register (SPI_ERR, Bit7) to supervise and preserve the data integrity. If an SPI protocol error is detected during a given frame, the SPI_ERR bit is set in the next SPI communication.

The SPI_ERR bit is set in the following error conditions:

- the number of SCLK clock pulses received when CSN is Low is not 0, or is not a multiple of 8 and at least 16
- the microcontroller sends an SPI command to an unused address. In particular, SDI stuck to High is reported in the SPI_ERR bit
- the LSB of an address byte is not set to 1. In particular, SDI stuck to Low is reported in the SPI_ERR bit
- the Last Address Bit Token (LABT, bit 1 of the address byte, see **Chapter 7.2**) in independent slave configuration is not set to 1
- the LABT bit of the last address byte in daisy chain configuration is not set to 1 (see **Chapter 7.3**)
- a clock polarity error is detected (see **Figure 17** Case 2 and Case 3): the incoming clock signal was High during CSN rising or falling edges.

For a correct SPI communication:

- SCLK must be Low for a minimum t_{BEF} before CSN falling edge and t_{lead} after CSN falling edge
- SCLK must be Low for a minimum t_{lag} before CSN rising edge and t_{BEH} after CSN rising edge



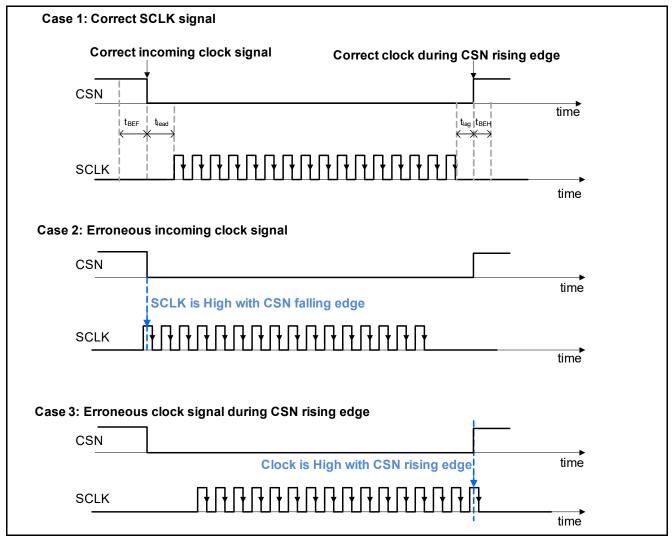


Figure 17 Clock Polarity Error



7.2 SPI with independent slave configuration

In an independent slave configuration, the microcontroller controls the CSN of each slave individually (**Figure 18**).

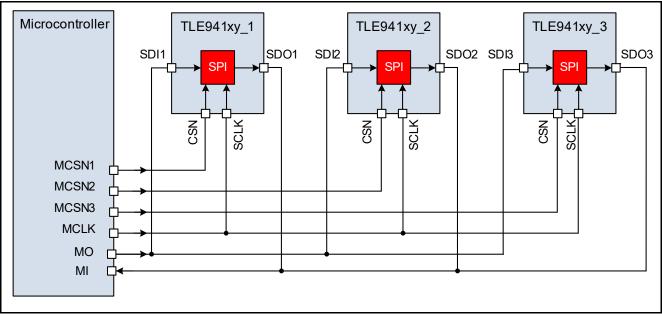


Figure 18 SPI with independent slave configuration

Each SPI communication starts with one address byte followed by one data byte (**Figure 19**). The LSB of the data byte must be set to '1'. The address bytes specifies:

- the type of operation: READ ONLY (OP bit =0) or READ/ WRITE (OP bit = 1) of the configuration bits, and READ ONLY (OP bit =0) or READ & CLEAR (OP bit = 1) of the status bits.
- The target register address (A[6:2])

The Last Address Byte Token bit (LABT, Bit1 of the address byte) must be set to 1, as no daisy chain configuration is used.

While the microcontroller sends the address byte on SDI, SDO shifts out GEF and the Global Status Register.

A further data byte (Bit15...8) is allocated to either configure the half-bridges or retrieve status information of the TLE94112ES.



	LSB			Addres	s Byte							Data	Byte			MSB
	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
SDI	1	LABT = 1	A2	A3	A4	A5	A6	OP	D0	D1	D2	D3	D4	D5	D6	D7
										Registe	er conter	nt of the	selectec	l addres	s	
	LSB		Glob	oal Stat	us Regi	ister					Data	a Byte ((Respoi	nse)		MSB
	LSB 0	1	Glob 2	oal Stati 3	us Regi 4	ister 5	6	7	8	9	Data 10	a Byte(11	(Respoi	nse) 13	14	MSB 15
SD0		1 TPW		3	4		-	7 SPI_ ERR	8 D0	9 D1		-			14 D6	

Figure 19 SPI Operation Mode with independent slave configuration

The in-frame response characteristic enables the microcontroller to read the contents of the addressed register within the SPI command. See **Figure 19**.



7.3 Daisy chain operation

The TLE94112ES supports daisy chain operation with devices with the same SPI protocol. This section describes the daisy chain hardware configuration with three devices from the TLE941xy family (See **Figure 20**).

The master output (noted MO) is connected to a slave SDI and the first slave SDO is connected to the next slave SDI to form a chain. The SDO of the final slave in the chain will be connected to the master input (MI) to close the loop of the SPI communication frame. In daisy chain configuration, a single chip select, CSN, and clock signal, SCLK, connected in parallel to each slave device, are used by the microcontroller to control or access the SPI devices.

In this configuration, the Master Output must send the address bytes and data bytes in the following order:

- All address bytes must be sent first:
 - Address Byte 1 (for TLE941xy_1) is sent first, followed by Address Byte 2 (for TLE941xy_2) etc,...
 - The LABT bit of the last address byte must be 1, while the LABT bit of all the other address bytes must be 0
- The data bytes are sent all together once all address bytes have been transmitted: Data Byte 1 (for TLE941xy_1) is sent first, followed by Data Byte 2 (for TLE941xy_2) etc,...

The Master Input (MI), which is connected to the SDO of the last device in the daisy chain receives:

- A logic OR combination of all Global Error Flags (GEF), at the beginning of the SPI frame, between CSN falling edge and the first SCLK rising edge
- The logic OR combination of the GEFs is followed by the Global Status Registers in reverse order. In other words MI receives first the Global Status Register of the last device of the daisy chain
- Once all Global Status Registers are received, MI receives the response bytes corresponding to the
 respective address and data bytes in reverse order. For example, if the daisy chain consists of three devices
 with SDO or TLE941xy_3 connected to MI, the master receives first the Response Byte 3 of TLE941xy_3
 (corresponding to Address Byte 3 and Data Byte 3) followed by the Response Byte 2 of TLE941xy_2 and
 finally the Response Byte 1 of TLE941xy_1.

An example of an SPI frame with three devices from the TLE941xy family is shown in **Figure 21**.

Note: The signal on the SDI pin of the first IC in daisy chain (and in non-daisy chain mode), must be Low at the beginning of the SPI frame (between CSN falling edge and the first SCLK rising edge). This is because each Global Error Flag in daisy chain operation is implemented in OR logic.



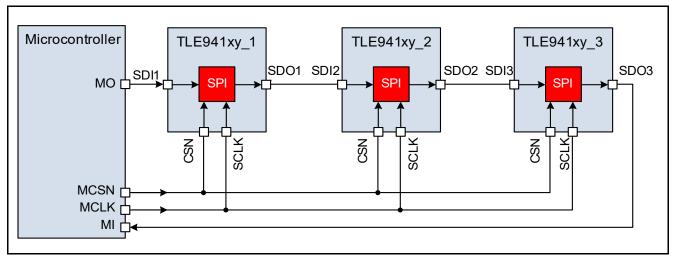


Figure 20 Example of daisy chain hardware configuration with devices from the TLE941xy family

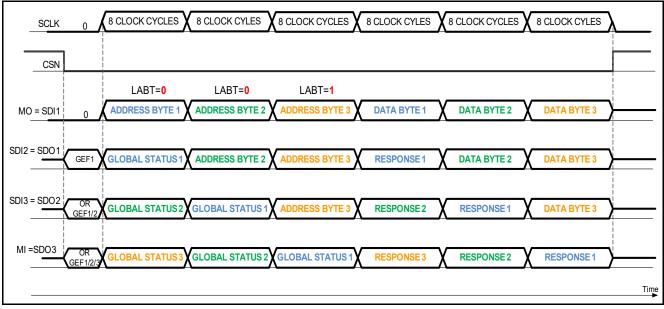


Figure 21 SPI frame with three devices of the TLE941xy family

Like in the individual slave configuration, it is possible to check if one or several TLE941xy have detected a fault condition by reading the logic OR combination of all the Global Error Flags when CSN goes Low without any clock cycle (**Figure 22**).



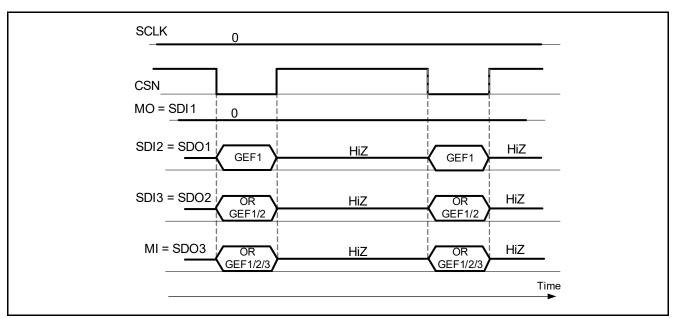


Figure 22 Global Error Flag with zero SCLK clock cycle in daisy chain consisting only of TLE941xy devices

Note: Some SPI protocol errors such as the LSB of an address byte is wrongly equal to 0, may be reported in the SPI_ERR bit of another device in the daisy chain (refer to **Chapter 7.1.3** and **Chapter 7.7** for more details on SPI_ERR). In this case some devices might accept wrong data during the corrupted SPI frame. Therefore if one of the devices in the daisy chain reports an SPI error, it is recommended to verify the content of the registers of all devices.

7.4 Status register change during SPI communication

If a new failure occurs after the transfer of the data byte(s), i.e. between the end of the last address byte and the CSN rising edge, this failure will be reported in the next SPI frame (see example in **Figure 23**).

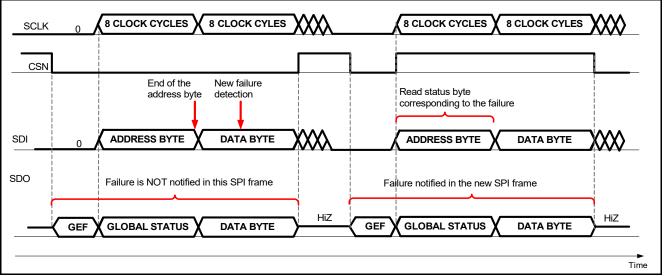


Figure 23 Status register change during transfer of data byte - Example in independent slave configuration



No information is lost, even if a status register is changed during a SPI frame, in particular during a Read and Clear command. For example:

- the microcontroller sends a Read and Clear command to a status register
- the TLE94112ES detects during the transfer the data byte(s) a new fault condition, which is normally reported in the target status register

The incoming Clear command will be ignored, so that the microcontroller can read the new failure in the subsequent SPI frames.

Data inconsistency between the Global Status Register (see **Chapter 7.7**) and the data byte (status register) within the same SPI frame is possible if:

- an open load or overcurrent error is detected during the transfer of the data byte
- the target status register corresponds to the new detected failure

In this case the new failure:

- is not reported in the Global Status Register of the current SPI frame but in the next one
- is reported in the data byte of the current SPI frame

Refer to Figure 23.



		Overo														
				Addree	ss Byte							Data	Byte			
	LSB 0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	MSB 15
SDI	1	LABT	A2 =0	A3 =0	A4 =1	A5 =1	A6 =0	OP =0	X	x	x	x	x	X	x	x
Overcurre	ont foilur	o dotoo	tod on	LIS of L		uring th										
ransfer of						unng un	5			Targ	jet stati	us regis	ter : O	C error	of HB	1-4
			•										·			
	LSB		1	-	tus Reg					r	1	Data B	i	<u> </u>	-	MSB
SDO	0	1	2	3	4	5	6 	7 SPI	8 D0	9 D1	10 D2	11 D3	12 D4	13 D5	14 D6	15 D7
000	0	TPW	ISD	NPOR	vs_ov	/vs_uv	=0	ERR	=0	=1	=0	=0	=0	=0	=0	=0
	Error bit	(Overc	urrent	or Oper	n Load					•		HB1 H	IS OC	roporto	the ne	\ A /
does n	iot repor					, ,	istenc	v betwee	en Globa	al Statu		Overcu				S of HB
does n –	lot repor					, ,		y betwee d target			ıs Regi	Overcu				
-	frame	t the ne	ew Ove		t failure	Incons	an		Status F	Registe	ıs Regi: r	Overcu ster	irrent fa			
-		t the ne	ew Ove		t failure	Incons	an	d target	Status F	Registe	ıs Regi: r	Overcu ster	irrent fa			
-		t the ne	w Ove		t failure	Incons SPI frar	an	d target	Status F	Registe	ıs Regi: r	Overcu ster	B 1-4)			
-	frame	t the ne 2 (nev	ew Ove	Addres	New set Solution	SPI frar	an ne:e.; 6	g. Read	Status F	Registe	ıs Regi: r	Overcu ster	B 1-4)			S of HB
-	frame	t the ne	w Ove	Addres	New ss Byte	Incons SPI frar	an ne:e.	g. Read	SYS_D	Registe	is Regis r OC err	Overcu ster or of HI	B 1-4) Byte	ailure o	I the F	S of HB
-	frame	t the ne 2 (nev	ew Ove	Addres	New Siss Byte	SPI fram 5 A5	an ne:e., 6 <u>A6</u>	g. Read	SYS_D	Registe IAG2 (9	IS Regis r OC err	Overcu ster or of HI Data	B 1-4) Byte	13	n the H	MSB 15
-	frame	t the ne 2 (nev	ew Ove	Addres	New Siss Byte	SPI fram 5 A5	an ne:e., 6 <u>A6</u>	g. Read	SYS_D	IAG2 (IS Regis	Overcu ster or of HI Data	B 1-4) Byte 12 X	13 X	14	MSB 15 X
-	frame	t the ne 2 (nev	ew Ove	Addres	New Siss Byte	SPI fram 5 A5	an ne:e., 6 <u>A6</u>	g. Read	SYS_D	IAG2 (IS Regis	Overcu ster or of HI Data	B 1-4) Byte 12 X	13 X	14	MSB 15 X
-	frame	t the ne 2 (nev	v)	Addres	New Siss Byte	SPI fram 5 A5 =1	an ne:e., 6 <u>A6</u>	g. Read	SYS_D	IAG2 (9 X ► Targ	IS Regis r OC err 10 X et statu	Overcu ster or of HI Data	B 1-4) Byte 12 X ter : OC	13 X Cerror	14 X of HB 1	MSB 15 X -4
-	frame	t the ne 2 (nev	v)	Addres	New States Byte	SPI fram 5 A5 =1	an ne:e., 6 <u>A6</u>	g. Read	SYS_D	IAG2 (9 X ► Targ	IS Regis r OC err 10 X et statu	Overcu ster or of HI Data 11 X is regist	B 1-4) Byte 12 X ter : OC	13 X Cerror	14 X of HB 1	MSB 15 X
-	frame	1 1 LABT =1	ew Ove v) 2 A2 =0 Glob 2	Addres Addres A3 =0 pal State 3	New 3 ss Byte 4 A4 =1 us Reg 4	SPI fran 5 A5 =1	an ne: e, 6 A6 =0	g. Read	SYS_D	IAG2 (9 X Targ Res	IS Regis	Overcu ster Data 11 X Is regist	B 1-4) Byte 12 X ter : OC	13 X C error YS_DIA	14 14 x of HB 1	MSB 15 X -4
-	frame LSB 0 1	1 1 LABT =1	ew Ove v) 2 A2 =0 Glob 2	Addres Addres A3 =0 pal State 3	New 3 ss Byte 4 A4 =1 us Reg 4	SPI fran 5 A5 =1 ister 5	an ne: e., 6 A6 =0 6 LE	g. Read	SYS_D	IAG2 (9 X Targ Res 9 D1	IS Regis r OC err 10 X et statu sponse 10 D2	Overcu ster Data 11 X Is regist Data B 11 D3	B 1-4) Byte 12 X ter : OC yte : S` 12 D4	13 X Cerror YS_DIA 13 D5	14 14 X of HB 1 AG 2 14 D6	MSB 15 X -4 MSB 15 D7

changed during the transfer of an address byte



7.5 SPI Bit Mapping

The SPI Registers have been mapped as shown in **Figure 25** and **Figure 26** respectively.

The control registers are READ/ WRITE registers. To set the control register to READ, bit 7 of the address byte (OP bit) must be programmed to '0', otherwise '1' for WRITE.

The status registers are READ/CLEAR registers. To CLEAR any Status Register, bit 7 of the address byte must be set to '1', otherwise '0' for READ.

	15	14	13	12	11	10	9	8	7	6543210
				8 Data Bit	s [D7D0]	1			8 Addre	ss Bits [A7…A0]
			for Cont	figuration 8					Access	
				•		ormation			type	
				_	_1_CTRL					0 0 0 0 0 LABT 1
_				_	_2_CTRL				read/write	1 0 0 0 0 LABT 1
S				_	<u>3_CTRL</u>				read/write	0 1 0 0 0 LABT 1
<u>~</u>				read/write	1 1 0 0 0 LABT 1					
Ош				read/write	0 0 1 0 0 LABT '					
2 F				read/write	1 0 1 0 0 LABT '					
s I				read/write	0 1 1 0 0 LABT 1					
U U U					DC_CTRL				read/write	1 1 1 0 0 LABT '
•					DC_CTRL				read/write	0 0 0 1 0 LABT 1
сщ ж				_	DC_CTRL				read/write	1 0 0 1 0 LABT 1
				_	L_CTRL				read/write	0 1 0 1 0 LABT 1
_					CTRL				read/write	1 1 0 1 0 LABT '
					G_CTRL				read	1 1 0 0 1 LABT
S			SY	S_DIAG_1	: Global sta	tus 1			read/clear	0 0 1 1 0 LABT [·]
s α S			SYS_[DIAG_2 : OF	PERROR_	1_STAT			read/clear	1 0 1 1 0 LABT '
			SYS_[DIAG_3 : OF	PERROR_2	2_STAT			read/clear	0 1 1 1 0 LABT ²
S.S			SYS_[DIAG_4 : OF	PERROR_	3_STAT			read/clear	1 1 1 1 0 LABT '
ப⊤			SYS_[DIAG_5 : OI	PERROR_4	4_STAT			read/clear	0 0 0 0 1 LABT [·]
ώu			SYS_[DIAG_6 : OI	PERROR_	5_STAT			read/clear	1 0 0 0 1 LABT
2			SYS [DIAG_7 : OF	PERROR	6_STAT			read/clear	0 1 0 0 1 LABT

Figure 25 TLE94112ES SPI Register mapping

Note: LABT: Last Address Bit Token, refer to Chapter 7.2 and Chapter 7.3.

-		ţ	:	ş	¢,	Ş	ş	•	•	,		4	•
Register Name	ame	CI	14	13	12 Data Bits D7	s D7D0	0	'n	ø	Add	0 2 4 3 2 Address Bits A7A0	з с А0	-
		D7	D6	D5	CONTROL	D3 REGISTERS	D2	Ы	DO	Access type			
HB_ACT_1_CTRL		HB4_HS_EN	HB4_LS_EN	HB3_HS_EN	HB3_LS_EN	HB2_HS_EN	HB2_LS_EN	HB1_HS_EN	HB1_LS_EN	read/write	0 0 0	0 0	LABT 1
HB_ACT_2_CTRL		HB8_HS_EN	HB8_LS_EN	HB7_HS_EN	HB7_LS_EN	HB6_HS_EN	HB6_LS_EN	HB5_HS_EN	HB5_LS_EN	read/write	0	0	LABT 1
HB_ACT_3_CTRL		HB12_HS_EN	HB12_LS_EN	HB11_HS_EN	HB11_LS_EN	HB10_HS_EN	HB10_LS_EN	HB9_HS_EN	HB9_LS_EN	read/write	0 1 0 1 0		LABT 1
		HB8 MODE1	HB8 MODE0	HB7 MODE1	HB7 MODE0	HB6 MODE1	HB6 MODE0	HB5 MODE1	HB5 MODE0	read/write	0 0 1	0	LABT 1
HB_MODE_3_CTRL		HB12_MODE1	HB12_MODE0	HB11_MODE1	HB11_MODE0	HB10_MODE1	HB10_MODE0	HB9_MODE1	HB9_MODE0	read/write		0	LABT 1
PWM_CH_FREQ_CTRL		FM_CLK_MOD1	FM_CLK_MOD0	PWM_CH3_FREQ_1	PWM_CH3_FREQ_0	PWM_CH2_FREQ_1	PWM_CH2_FREQ_0			read/write	0 1 1	0 0	LABT 1
		PWM1_DC_CTRL_7	PWM1_DC_CTRL_6	PWM1_DC_CTRL_5	PWM1_DC_CTRL_4	PWM1_DC_CTRL_3	PWM1_DC_CTRL_2	PWM1_DC_CTRL_1	PWM1_DC_CTRL_0		1 1 1	0 0	LABT 1
R PWM2_DC_CTRL		PWM2_DC_CTRL_7	PWM2_DC_CTRL_6	PWM2_DC_CTRL_5	PWM2_DC_CTRL_6 PWM2_DC_CTRL_5 PWM2_DC_CTRL_4 PWM3_DC_CTRL_6 PWM3_DC_CTRL_5 PWM3_DC_CTRL_4	PWM2_DC_CTRL_3	PWM2_DC_CTRL_2	PWM2_DC_CTRL_1	PWM2_DC_CTRL_0	read/write read/write	0 0	1 0	LABT 1
FW OL CTRL		FW HB6	FW HB5	FW HB4	FW HB3	FW HB2	FW HB1	OI SFI HS2	OL SFL HS1		, 1	0	LABT 1
FW CTRL		reserved	reserved	FW HB12	FW HB11	FW HB10	FW HB9	FW HB8	FW HB7	read/write	· -		LABT 1
CONFIG_CTRL		reserved	reserved	reserved	reserved	reserved	DEV_ID2	DEV_ID1	DEV_ID0	read	1 1 0		LABT 1
					STATUS	REGISTERS							
	tus 1	SPI_ERR	LE	M_SV	VS_0V	NPOR	TSD	TPW	0	read/clear	0	0	LABT 1
SYS_DIAG_2 : OP ERROR_1_STAT SYS_DIAG_3 : OP ERROR_3 STAT	₹_1_STAT ₹ 2_STAT	HB4_HS_OC HB8_HS_OC	HB4_LS_OC HB8_LS_OC	HB3_HS_OC	HB3_LS_OC HR7_LS_OC	HB2_HS_OC HB6_HS_OC	HB2_LS_OC HB6_LS_OC	HB1_HS_OC HB5_HS_OC	HB1_LS_OC HB5_LS_OC	read/clear	1 0 1	1 1	LABT 1
	R 3 STAT	HB12 HS OC	HB12 LS OC	HB11 HS OC	HB11 LS OC	HB10 HS OC	HB10 LS OC	HB9 HS OC	HB9 IS OC	read/clear	•		I ABT 1
SYS_DIAG_5 : OP ERROR_4_STAT	R_4_STAT	HB4_HS_OL	HB4_LS_OL	HB3_HS_OL	HB3_LS_OL	HB2_HS_OL	HB2_LS_OL	HB1_HS_OL	HB1_LS_OL	read/clear	0 0 0		LABT 1
2 SYS_DIAG_6 : OP ERROR_5_STAT	R_5_STAT	HB8_HS_OL	HB8_LS_OL	HB7_HS_OL	HB7_LS_OL	HB6_HS_OL	HB6_LS_OL	HB5_HS_OL	HB5_LS_OL	read/clear	1 0 0	0 1 1	LABT 1
SYS_DIAG_7 : OP ERROR_6_STAT	₹_6_STAT	HB12_HS_OL	HB12_LS_OL	HB11_HS_OL	HB11_LS_OL	HB10_HS_OL	HB10_LS_OL	HB9_HS_OL	HB9_LS_OL	read/clear	0 1 0	0 1 1	LABT 1

Figure 26 TLE94112ES Bit Mapping

Note: LABT: Last Address Bit Token, refer to Chapter 7.2 and Chapter 7.3.





7.6 SPI Control Registers

The Control Registers have a READ/WRITE access (see **Chapter 7.5**):

- The 'POR' value is defined by the register content after a POR or device Reset
 - The default value of all control registers is $0000 0000_B$
- One 16-bit SPI command consists of two bytes (see Figure 25 and Figure 26), i.e.
 - an address byte
 - followed by a data byte
- The control bits are not cleared or changed automatically by the device. This must be done by the microcontroller via SPI programming.
- Reading a register is done byte wise by setting the SPI bit 7 to "0" (= READ ONLY).
- Writing to a register is done byte wise by setting the SPI bit 7 to "1".



7.6.1 Control register definition

HB_ACT_1_CTRL

Half-bridge output control 1 (Address Byte [OP] 000 00[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB4_HS_EN	HB4_LS_EN	HB3_HS_EN	HB3_LS_EN	HB2_HS_EN	HB2_LS_EN	HB1_HS_EN	HB1_LS_EN
rw							

Field	Bits	Туре	Description
HB4_HS_EN	D7	rw	Half-bridge output 4 high side switch enable0BHS4 OFF/ High-Z (default value)1BHS4 ON
HB4_LS_EN	D6	rw	Half-bridge output 4 low side switch enable00BLS4 OFF/ High-Z (default value)11BLS4 ON
HB3_HS_EN	D5	rw	Half-bridge output 3 high side switch enable0HS3 OFF/ High-Z (default value)1HS3 ON
HB3_LS_EN	D4	rw	Half-bridge output 3 low side switch enable0BLS3 OFF/ High-Z (default value)1BLS3 ON
HB2_HS_EN	D3	rw	Half-bridge output 2 high side switch enable0HS2 OFF/ High-Z (default value)1HS2 ON
HB2_LS_EN	D2	rw	Half-bridge output 2 low side switch enable0BLS2 OFF/ High-Z (default value)1BLS2 ON
HB1_HS_EN	D1	rw	Half-bridge output 1 high side switch enable0HS1 OFF/ High-Z (default value)1HS1 ON
HB1_LS_EN	DO	rw	Half-bridge output 1 low side switch enable001LS1 OFF/ High-Z (default value)1LS1 ON

Note: The simultaneous activation of both HS and LS switch within a half-bridge is prevented by the digital block to avoid cross current. If both LS_EN and HS_EN bits of a given half-bridge are set, the logic turns off this half-bridge.



HB_ACT_2_CTRL

Half-bridge output control 2 (Address Byte $[OP]100 00[LABT]1_B$)

D7	D6	D5	D4	D3	D2	D1	D0
HB8_HS_EN	HB8_LS_EN	HB7_HS_EN	HB7_LS_EN	HB6_HS_EN	HB6_LS_EN	HB5_HS_EN	HB5_LS_EN
rw							

Field	Bits	Туре	Description
HB8_HS_EN	D7	rw	Half-bridge output 8 high side switch enable0BHS8 OFF/ High-Z (default value)1BHS8 ON
HB8_LS_EN	D6	rw	Half-bridge output 8 low side switch enable00BLS8 OFF/ High-Z (default value)1LS8 ON
HB7_HS_EN	D5	rw	Half-bridge output 7 high side switch enable0BHS7 OFF/ High-Z (default value)1BHS7 ON
HB7_LS_EN	D4	rw	Half-bridge output 7 low side switch enable00BLS7 OFF/ High-Z (default value)11BLS7 ON
HB6_HS_EN	D3	rw	Half-bridge output 6 high side switch enable0BHS6 OFF/ High-Z (default value)1BHS6 ON
HB6_LS_EN	D2	rw	Half-bridge output 6 low side switch enable0BLS6 OFF/ High-Z (default value)1BLS6 ON
HB5_HS_EN	D1	rw	Half-bridge output 5 high side switch enable0HS5 OFF/ High-Z (default value)1HS5 ON
HB5_LS_EN	DO	rw	Half-bridge output 5 low side switch enable0LS5 OFF/ High-Z (default value)1LS5 ON

Note: The simultaneous activation of both HS and LS switch within a half-bridge is prevented by the digital block to avoid cross current. If both LS_EN and HS_EN bits of a given half-bridge are set, the logic turns off this half-bridge.



HB_ACT_3_CTRL

Half-bridge output control 3 (Address Byte $[OP]010 00[LABT]1_B$)

D7	D6	D5	D4	D3	D2	D1	D0
HB12_HS_EN	HB12_LS_EN	HB11_HS_EN	HB11_LS_EN	HB10_HS_EN	HB10_LS_EN	HB9_HS_EN	HB9_LS_EN
rw	rw	rw	rw	rw	rw	rw	rw

Field	Bits	Туре	Description
HB12_HS_EN	D7	rw	Half-bridge output 12 high side switch enable0BHS12 OFF/ High-Z (default value)1BHS12 ON
HB12_LS_EN	D6	rw	Half-bridge output 12 low side switch enable0LS12 OFF/ High-Z (default value)1LS12 ON
HB11_HS_EN	D5	rw	Half-bridge output 11 high side switch enable0HS11 OFF/ High-Z (default value)1HS11 ON
HB11_LS_EN	D4	rw	Half-bridge output 11 low side switch enable0LS11 OFF/ High-Z (default value)1LS11 ON
HB10_HS_EN	D3	rw	Half-bridge output 10 high side switch enable0HS10 OFF/ High-Z (default value)1HS10 ON
HB10_LS_EN	D2	rw	Half-bridge output 10 low side switch enable0BLS10 OFF/ High-Z (default value)1BLS10 ON
HB9_HS_EN	D1	rw	Half-bridge output 9 high side switch enable0HS9 OFF/ High-Z (default value)1HS9 ON
HB9_LS_EN	D0	rw	Half-bridge output 9 low side switch enable0BLS9 OFF/ High-Z (default value)1BLS9 ON

Note: The simultaneous activation of both HS and LS switch within a half-bridge is prevented by the digital block to avoid cross current. If both LS_EN and HS_EN bits of a given half-bridge are set, the logic turns off this half-bridge.



HB_MODE_1_CTRL Half-bridge output mode control 1 (Address Byte [OP]110 00[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB4_MODE1	HB4_MODE0	HB3_MODE1	HB3_MODE0	HB2_MODE1	HB2_MODE0	HB1_MODE1	HB1_MODE0
rw							

Field	Bits	Туре	Description
HB4_MODEn	D7:D6	rw	Half-bridge output 4 mode select
(n = 0,1)			00 _B No PWM (default value)
			01 _B PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3
HB3_MODEn	D5:D4	rw	Half-bridge output 3 mode select
(n = 0,1)			00 _B No PWM (default value)
			01 _B PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3
HB2_MODEn	D3:D2	rw	Half-bridge output 2 mode select
(n = 0,1)			00 _B No PWM (default value)
			01 _B PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3
HB1_MODEn	D1:D0	rw	Half-bridge output 1 mode select
(n = 0,1)			00 _B No PWM (default value)
			01 _B PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3



HB_MODE_2_CTRL Half-bridge output mode control 2 (Address Byte [OP]00

Half-bridge output mode control 2 (Address Byte [OP]001 00[LABT] 1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB8_MODE1	HB8_MODE0	HB7_MODE1	HB7_MODE0	HB6_MODE1	HB6_MODE0	HB5_MODE1	HB5_MODE0
rw							

Field	Bits	Туре	Description
HB8_MODEn (n = 0,1)	D7:D6	rw	Half-bridge output 8 mode select 00_B No PWM (default value) 01_B PWM control with PWM Channel 1 10_B PWM control with PWM Channel 2 11_B PWM control with PWM Channel 3
HB7_MODEn (n = 0,1)	D5:D4	rw	Half-bridge output 7 mode select 00_B No PWM (default value) 01_B PWM control with PWM Channel 1 10_B PWM control with PWM Channel 2 11_B PWM control with PWM Channel 3
HB6_MODEn (n = 0,1)	D3:D2	rw	Half-bridge output 6 mode select 00_B No PWM (default value) 01_B PWM control with PWM Channel 1 10_B PWM control with PWM Channel 2 11_B PWM control with PWM Channel 3
HB5_MODEn (n = 0,1)	D1:D0	rw	Half-bridge output 5 mode select 00_B No PWM (default value) 01_B PWM control with PWM Channel 1 10_B PWM control with PWM Channel 2 11_B PWM control with PWM Channel 3



HB_MODE_3_CTRL Half-bridge output mode control 3 (Address Byte [OP]101 00[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB12_MODE1	HB12_MODE0	HB11_MODE1	HB11_MODE0	HB10_MODE1	HB10_MODE0	HB9_MODE1	HB9_MODE0
rw	rw	rw	rw	rw	rw	rw	rw

Field	Bits	Туре	Description
HB12_MODEn	D7:D6	rw	Half-bridge output 12 mode select
(n = 0,1)			00 _B No PWM (default value)
			01 _B PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3
HB11_MODEn	D5:D4	rw	Half-bridge output 11 mode select
(n = 0,1)			00 _B No PWM (default value)
			01 _B PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3
HB10_MODEn	D3:D2	rw	Half-bridge output 10 mode select
(n = 0,1)			00 _B No PWM (default value)
			01 _B PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3
HB9_MODEn	D1:D0	rw	Half-bridge output 9 mode select
(n = 0,1)			00 _B No PWM (default value)
			01_{B} PWM control with PWM Channel 1
			10 _B PWM control with PWM Channel 2
			11 _B PWM control with PWM Channel 3



PWM_CH_FREQ_CTRL PWM channel frequency select (Address Byte [OP]011 00[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
FM_CLK_ MOD1	FM_CLK_ MOD0	PWM_CH3_F REQ_1	PWM_CH3_F REQ_0	PWM_CH2_F REQ_1	PWM_CH2_F REQ_0	PWM_CH1_F REQ_1	PWM_CH1_F REQ_0
rw	rw	rw	rw	rw	rw	rw	rw

Field	Bits	Туре	Description
FM_MOD_EN	D7:D6	rw	FM Modulation Enable ¹⁾
			00 _B No modulation (default)
			01 _B Modulation frequency 15.625kHz
			10 _B Modulation frequency 31.25kHz
			11 _B Modulation frequency 62.5kHz
PWM_CH3_FREQ_	D5:D4	rw	PWM Channel 3 frequency select
n (n=0,1)			00 _B PWM is stopped and off (default value)
			01 _B PWM frequency 1:80Hz
			10 _B PWM frequency 2 : 100Hz
			11 _B PWM frequency 3 : 200Hz
PWM_CH2_FREQ_	D3:D2	rw	PWM Channel 2 frequency select
n (n=0,1)			00 _B PWM is stopped and off (default value)
			01 _B PWM frequency 1 : 80Hz
			10 _B PWM frequency 2 : 100Hz
			11 _B PWM frequency 3 : 200Hz
PWM_CH1_FREQ_	D1:D0	rw	PWM Channel 1 frequency select
n (n=0,1)			00 _B PWM is stopped and off (default value)
			01 _B PWM frequency 1:80Hz
			10 _B PWM frequency 2 : 100Hz
			11 _B PWM frequency 3 : 200Hz

1) Not subject to production test, guaranteed by design. Frequency may deviate by ±10%



PWM1_DC_CTRL PWM channel 1 duty cycle configuration (Address Byte [OP]111 00[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
PWM1_DC_ CTRL_7	PWM1_DC_ CTRL_6	PWM1_DC_ CTRL_5	PWM1_DC_ CTRL_4	PWM1_DC_ CTRL_3	PWM1_DC_ CTRL_2	PWM1_DC_ CTRL_1	PWM1_DC_ CTRL_0
rw							

Field	Bits	Туре	Description
PWM1_DC_CTRLn	D7:D0	rw	PWM Channel 1 Duty Cycle configuration (bit7=MSB; bit0)
			0000 0000 _B 100% OFF (default value) xxxx xxxx _B parts of 255 ON 1111 1111 _B 100% ON

Note: Refer to **Chapter 6.1.1** for more information on PWM operation

PWM2_DC_CTRL PWM channel 2 duty cycle configuration (Address [OP]000 10[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
PWM2_DC_ CTRL_7	PWM2_DC_ CTRL_6	PWM2_DC_ CTRL_5	PWM2_DC_ CTRL_4	PWM2_DC_ CTRL_3	PWM2_DC_ CTRL_2	PWM2_DC_ CTRL_1	PWM2_DC_ CTRL_0
rw							

Field	Bits	Туре	Description
PWM2_DC_CTRLn	D7:D0	rw	PWM Channel 2 Duty Cycle configuration (bit7=MSB; bit0)
			0000 0000 _B 100% OFF (default value) xxxx xxxx _B parts of 255 ON 1111 1111 _B 100% ON



$\label{eq:pwm3_DC_CTRL} PWM3_DC_CTRL \\ PWM \ channel \ 3 \ duty \ cycle \ configuration \ (Address \ Byte \ [OP]100 \ 10[LABT]1_B) \\ \end{array}$

D7	D6	D5	D4	D3	D2	D1	D0
PWM3_DC_ CTRL_7	PWM3_DC_ CTRL_6	PWM3_DC_ CTRL_5	PWM3_DC_ CTRL_4	PWM3_DC_ CTRL_3	PWM3_DC_ CTRL_2	PWM3_DC_ CTRL_1	PWM3_DC_ CTRL_0
rw							

Field	Bits	Туре	Description
PWM3_DC_CTRLn	D7:D0	rw	PWM Channel 3 Duty Cycle configuration (bit7=MSB;
			bit0)
			0000 0000 _B 100% OFF (default value)
			xxxx xxxx _B parts of 255 ON
			1111 1111 _B 100% ON



FW_OL_CTRL

Free-wheeling configuration and Open load detection setting of HS1 and HS2 (Address Byte [OP]010 10[LABT] 1_B)

D7	D6	D5	D4	D3	D2	D1	D0
FW_HB6	FW_HB5	FW_HB4	FW_HB3	FW_HB2	FW_HB1	OL_SEL_HS2	OL_SEL_HS1
rw	rw						

Field	Bits	Туре	Description
FW_HB6	D7	rw	HB6 free-wheeling configuration00BPassive free-wheeling (default value)1Active free-wheeling
FW_HB5	D6	rw	HB5 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling
FW_HB4	D5	rw	HB4 free-wheeling configuration 00BPassive free-wheeling (default value)1Active free-wheeling
FW_HB3	D4	rw	HB3 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling
FW_HB2	D3	rw	HB2 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling
FW_HB1	D2	rw	HB1 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling
OL_SEL_HS2	D1	rw	HS2 open load detection current and filter time select0High-current mode (default value)1LED Mode (Low current mode)
OL_SEL_HS1	DO	rw	HS1 open load detection current and filter time select 0_B High current mode (default value) 1_B LED Mode (Low current mode)



FW_CTRL

Free-wheeling configuration (Address Byte [OP]110 10[LABT]1)_B

D7	D6	D5	D4	D3	D2	D1	D0
reserved	reserved	FW_HB12	FW_HB11	FW_HB10	FW_HB9	FW_HB8	FW_HB7
rw	rw	rw	rw	rw	rw	rw	rw

Field	Bits	Туре	Description				
reserved	D7:D6	rw	To be programmed as '0'.				
FW_HB12	D5	rw	HB12 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling				
FW_HB11	D4	rw	HB11 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling				
FW_HB10	D3	rw	HB10 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling				
FW_HB9	D2	rw	HB9 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling				
FW_HB8	D1	rw	HB8 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling				
FW_HB7	D0	rw	HB7 free-wheeling configuration0BPassive free-wheeling (default value)1BActive free-wheeling				



CONFIG_CTRL

Device Configuration control (Address Byte [OP]110 01[LABT] 1_B)

D7	D6	D5	D4	D3	D2	D1	D0
reserved	reserved	reserved	reserved	reserved	DEV_ID2	DEV_ID1	DEV_ID0
r	r	r	r	r	r	r	r

Field	Bits	Туре	Description					
reserved	D7:D3	r	Always reads as '0'					
DEV_IDn	D2:D0	r	Device/ derivative identifier					
			Note: These bits can be used to verify the silicon content of the device					
			000 _B TLE94112EL/ES chip 001 _B TLE94110EL/ES chip					
			$010_{\rm B}$ TLE94108EL/ES chip					
			011 _B TLE94106EL/ES chip					
			100 _B TLE94104EP chip					
			101 _B TLE94103EP chip					
			110 _B reserved					
			111 _B reserved					



7.7 SPI Status Registers

The Control Registers have a READ/CLEAR access (see also **Chapter 7.5**):

- The 'POR Value' of the Status registers (content after a POR or device Reset) and is 0000 0000_B.
- One 16-bit SPI command consists of two bytes (see Figure 25 and Figure 26), i.e.
 - an address byte
 - followed by a data byte
- Reading a register is done byte wise by setting the SPI bit 7 of the address byte to "0" (= Read Only).
- Clearing a register is done byte wise by setting the SPI bit 7 of the address byte to "1".
- SPI status registers are not cleared automatically by the device. This must be done by the microcontroller via SPI command.



7.7.1 Status register definition

SYS_DIAG1

Global status 1 (Address Byte [OP]001 10[LABT]1_B)

	D7	D6	D5	D4	D3	D2	D1	D0
	SPI_ERR	LE	VS_UV	vs_ov	NPOR	TSD	TPW	reserved
-	rc	r	rc	rc	rc	rc	rc	r

Field	Bits	Туре	Description					
SPI_ERR	D7	rc	SPI error detection 0_B No SPI protocol error is detected (default value). 1_B An SPI protocol error is detected.					
LE	D6	r	Load error detection (logic OR combination of Open Load and Overcurrent) 0 _B No Open Load and no Overcurrent detected (default value) 1 _B Open Load or Overcurrent detected in at least one of the power outputs. Error latched. Faulty output is latched off in case of Overcurrent					
VS_UV	D5	rc	VS Undervoltage error detection0BNo undervoltage on Vs detected (default value)1BUndervoltage on Vs detected. Error latched and all outputs disabled.					
VS_OV	D4	rc	VS Overvoltage error detection0BNo overvoltage on Vs detected (default value)1BOvervoltage on Vs detected. Error latched and all outputs disabled.					
NPOR	D3	rc	Not Power On Reset (NPOR) detection0BPOR on EN or VDD supply rail (default value)1BNo POR					
TSD	D2	rc	 Temperature shutdown error detection 0_B Junction temperature below temperature shutdown threshold (default value) 1_B Junction temperature has reached temperature shutdown threshold. Error latched and all outputs disabled. 					
TPW	D1	rc	 Temperature pre-warning error detection O_B Junction temperature below temperature pre-warning threshold (default value) 1_B Junction temperature has reached temperature pre-warning threshold. 					
reserved	D0	r	Bit reserved. Always reads '0'.					

Note: The LE bit in the Global Status register is read only. It reflects an OR combination of the respective open load and overcurrent errors of the half-bridge channels. If all OC/OL bits of the respective high-side and low-side channels are cleared to '0', the LE bit will be automatically updated to '0'.

SYS_DIAG_2 : OP_ERROR_1_STAT Overcurrent error status of half-bridge outputs 1 - 4 (Address Byte [OP]101 10[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB4_HS_OC	HB4_LS_OC	HB3_HS_OC	HB3_LS_OC	HB2_HS_OC	HB2_LS_OC	HB1_HS_OC	HB1_LS_OC
rc							

Field	Bits	Туре	Description
HB4_HS_OC	D7	rc	 High-side (HS) switch of half-bridge 4 overcurrent detection 0_B No error on HS4 switch (default value) 1_B Overcurrent detected on HS4 switch. Error latched and HS4 disabled.
HB4_LS_OC	D6	rc	Low-side (LS) switch of half-bridge 4 overcurrent detection0No error on LS4 switch (default value)1Overcurrent detected on LS4 switch. Error latched and LS4 disabled.
HB3_HS_OC	D5	rc	 High-side (HS) switch of half-bridge 3 overcurrent detection 0_B No error on HS3 switch (default value) 1_B Overcurrent detected on HS3 switch. Error latched and HS3 disabled.
HB3_LS_OC	D4	rc	Low-side (LS) switch of half-bridge 3 overcurrent detection0BNo error on LS3 switch (default value)1BOvercurrent detected on LS3 switch. Error latched and LS3 disabled.
HB2_HS_OC	D3	rc	 High-side (HS) switch of half-bridge 2 overcurrent detection 0_B No error on HS2 switch (default value) 1_B Overcurrent detected on HS2 switch. Error latched and HS2 disabled.
HB2_LS_OC	D2	rc	Low-side (LS) switch of half-bridge 2 overcurrent detection0BNo error on LS2 switch (default value)1BOvercurrent detected on LS2 switch. Error latched and LS2 disabled.
HB1_HS_OC	D1	rc	 High-side (HS) switch of half-bridge 1 overcurrent detection 0_B No error on HS1 switch (default value) 1_B Overcurrent detected on HS1 switch. Error latched and HS1 disabled.
HB1_LS_OC	DO	rc	Low-side (LS) switch of half-bridge 1 overcurrent detection0BNo error on LS1 switch (default value)1BOvercurrent detected on LS1 switch. Error latched and LS1 disabled.

SYS_DIAG_3 : OP_ERROR_2_STAT Overcurrent error status of half-bridge outputs 5 - 8 (Address Byte [OP]011 10[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB8_HS_OC	HB8_LS_OC	HB7_HS_OC	HB7_LS_OC	HB6_HS_OC	HB6_LS_OC	HB5_HS_OC	HB5_LS_OC
rc							

Field	Bits	Туре	Description				
HB8_HS_OC	D7	rc	 High-side (HS) switch of half-bridge 8 overcurrent detection 0_B No error on HS8 switch (default value) 1_B Overcurrent detected on HS8 switch. Error latched and HS8 disabled. 				
HB8_LS_OC	D6	rc	Low-side (LS) switch of half-bridge 8 overcurrent detection00BNo error on LS8 switch (default value)10Overcurrent detected on LS8 switch. Error latched and LS8 disabled.				
HB7_HS_OC	D5	rc	 High-side (HS) switch of half-bridge 7 overcurrent detection 0_B No error on HS7 switch (default value) 1_B Overcurrent detected on HS7 switch. Error latched and HS7 disabled. 				
HB7_LS_OC	D4	rc	Low-side (LS) switch of half-bridge 7 overcurrent detection0BNo error on LS7 switch (default value)1BOvercurrent detected on LS7 switch. Error latched and LS7 disabled.				
HB6_HS_OC	D3	rc	 High-side (HS) switch of half-bridge 6 overcurrent detection 0_B No error on HS6 switch (default value) 1_B Overcurrent detected on HS6 switch. Error latched and HS6 disabled. 				
HB6_LS_OC	D2	rc	Low-side (LS) switch of half-bridge 6 overcurrent detection00BNo error on LS6 switch (default value)10Overcurrent detected on LS6 switch. Error latched and LS6 disabled.				
HB5_HS_OC	D1	rc	 High-side (HS) switch of half-bridge 5 overcurrent detection 0_B No error on HS5 switch (default value) 1_B Overcurrent detected on HS5 switch. Error latched and HS5 disabled. 				
HB5_LS_OC	DO	rc	Low-side (LS) switch of half-bridge 5 overcurrent detection0BNo error on LS5 switch (default value)1BOvercurrent detected on LS5 switch. Error latched and LS5 disabled.				

SYS_DIAG_4 : OP_ERROR_3_STAT Overcurrent error status of half-bridge outputs 9 - 12(Address Byte [OP]111 10[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB12_HS_OC	HB12_LS_OC	HB11_HS_OC	HB11_LS_OC	HB10_HS_OC	HB10_LS_OC	HB9_HS_OC	HB9_LS_OC
rc	rc	rc	rc	rc	rc	rc	rc

Field	Bits	Туре	Description
HB12_HS_OC D7 rc			 High-side (HS) switch of half-bridge 12 overcurrent detection 0_B No error on HS12 switch (default value) 1_B Overcurrent detected on HS12 switch. Error latched and HS12 disabled.
HB12_LS_OC	D6	Low-side (LS) switch of half-bridge 12 overcurrent detection0BNo error on LS12 switch (default value)1BOvercurrent detected on LS12 switch. Error latched and LS12 disabled.	
HB11_HS_OC	D5	rc	 High-side (HS) switch of half-bridge 11 overcurrent detection 0_B No error on HS11 switch (default value) 1_B Overcurrent detected on HS11 switch. Error latched and HS11 disabled.
HB11_LS_OC	D4	rc	Low-side (LS) switch of half-bridge 11 overcurrent detection0BNo error on LS11 switch (default value)1BOvercurrent detected on LS11 switch. Error latched and LS11 disabled.
HB10_HS_OC	D3	rc	 High-side (HS) switch of half-bridge 10 overcurrent detection 0_B No error on HS10 switch (default value) 1_B Overcurrent detected on HS10 switch. Error latched and HS10 disabled.
HB10_LS_OC	D2	rc	Low-side (LS) switch of half-bridge 10 overcurrent detection0BNo error on LS10 switch (default value)1BOvercurrent detected on LS10 switch. Error latched and LS10 disabled.
HB9_HS_OC	D1	rc	 High-side (HS) switch of half-bridge 9 overcurrent detection 0_B No error on HS9 switch (default value) 1_B Overcurrent detected on HS9 switch. Error latched and HS9 disabled.
HB9_LS_OC	DO	rc	 Low-side (LS) switch of half-bridge 9 overcurrent detection 0_B No error on LS9 switch (default value) 1_B Overcurrent detected on LS9 switch. Error latched and LS9 disabled.

Note: Unused or not connected outputs for lower derivatives, i.e. TLE94110ES, TLE94108ES and TLE94106ES will be defined as 'reserved', always reads as '0'

SYS_DIAG_5 : OP_ERROR_4_STAT Open load error status of half-bridge outputs 1 - 4 (Address Byte [OP]000 01[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB4_HS_OL	HB4_LS_OL	HB3_HS_OL	HB3_LS_OL	HB2_HS_OL	HB2_LS_OL	HB1_HS_OL	HB1_LS_OL
rc							

Field	Bits	Туре	Description
HB4_HS_OL	D7	rc	High-side (HS) switch of half-bridge 4 open load detection0BNo error on HS4 switch (default value)1BOpen load detected on HS4 switch. Error latched.
HB4_LS_OL	D6	rc	Low-side (LS) switch of half-bridge 4 open load detection 0_B No error on LS4 switch (default value) 1_B Open load detected on LS4 switch. Error latched.
HB3_HS_OL	D5	rc	 High-side (HS) switch of half-bridge 3 open load detection 0_B No error on HS3 switch (default value) 1_B Open load detected on HS3 switch. Error latched.
HB3_LS_OL	D4	rc	Low-side (LS) switch of half-bridge 3 open load detection0BNo error on LS3 switch (default value)1BOpen load detected on LS3 switch. Error latched.
HB2_HS_OL	D3	rc	High-side (HS) switch of half-bridge 2 open load detection0BNo error on HS2 switch (default value)1BOpen load detected on HS2 switch. Error latched.
HB2_LS_OL	D2	rc	Low-side (LS) switch of half-bridge 2 open load detection 0_B No error on LS2 switch (default value) 1_B Open load detected on LS2 switch. Error latched.
HB1_HS_OL	D1	rc	High-side (HS) switch of half-bridge 1 open load detection0BNo error on HS1 switch (default value)1BOpen load detected on HS1 switch. Error latched.
HB1_LS_OL	DO	rc	Low-side (LS) switch of half-bridge 1 open load detection 0_B No error on LS1 switch (default value) 1_B Open load detected on LS1 switch. Error latched.

SYS_DIAG_6 : OP_ERROR_5_STAT Open load error status of half-bridge outputs 5 - 8 (Address Byte [OP]100 01[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB8_HS_OL	HB8_LS_OL	HB7_HS_OL	HB7_LS_OL	HB6_HS_OL	HB6_LS_OL	HB5_HS_OL	HB5_LS_OL
rc							

Field	Bits	Туре	Description					
HB8_HS_OL	D7	rc	High-side (HS) switch of half-bridge 8 open load detection00BNo error on HS8 switch (default value)10Deen load detected on HS8 switch. Error latched.					
HB8_LS_OL	D6	rc	Low-side (LS) switch of half-bridge 8 open load detection 0_B No error on LS8 switch (default value) 1_B Open load detected on LS8 switch. Error latched.					
HB7_HS_OL	D5	rc	High-side (HS) switch of half-bridge 7 open load detection0No error on HS7 switch (default value)1Open load detected on HS7 switch. Error latched.					
HB7_LS_OL	D4	rc	Low-side (LS) switch of half-bridge 7 open load detection0BNo error on LS7 switch (default value)1BOpen load detected on LS7 switch. Error latched.					
HB6_HS_OL	D3	rc	$High-side (HS)$ switch of half-bridge 6 open load detection 0_B No error on HS6 switch (default value) 1_B Open load detected on HS6 switch. Error latched.					
HB6_LS_OL	D2	rc	Low-side (LS) switch of half-bridge 6 open load detection 0_B No error on LS6 switch (default value) 1_B Open load detected on LS6 switch. Error latched.					
HB5_HS_OL	D1	rc	High-side (HS) switch of half-bridge 5 open load detection 0_B No error on HS5 switch (default value) 1_B Open load detected on HS5 switch. Error latched.					
HB5_LS_OL	DO	rc	Low-side (LS) switch of half-bridge 5 open load detection 0_B No error on LS5 switch (default value) 1_B Open load detected on LS5 switch. Error latched.					

SYS_DIAG_7 : OP_ERROR_6_STAT Open load error status of half-bridge outputs 9 - 12 (Address Byte [OP]010 01[LABT]1_B)

D7	D6	D5	D4	D3	D2	D1	D0
HB12_HS_OL	HB12_LS_OL	HB11_HS_OL	HB11_LS_OL	HB10_HS_OL	HB10_LS_OL	HB9_HS_OL	HB9_LS_OL
rc	rc	rc	rc	rc	rc	rc	rc

Field	Bits	Туре	Description
HB12_HS_OL	D7	rc	High-side (HS) switch of half-bridge 12 open load detection
			0 _B No error on HS12 switch (default value)
			1 _B Open load detected on HS12 switch. Error latched.
HB12_LS_OL	D6	rc	Low-side (LS) switch of half-bridge 12 open load detection
			0 _B No error on LS12 switch (default value)
			1 _B Open load detected on LS12 switch. Error latched.
HB11_HS_OL	D5	rc	High-side (HS) switch of half-bridge 11 open load detection
			0 _B No error on HS11 switch (default value)
			1 _B Open load detected on HS11 switch. Error latched.
HB11_LS_OL	D4	rc	Low-side (LS) switch of half-bridge 11 open load detection
			0 _B No error on LS11 switch (default value)
			1 _B Open load detected on LS11 switch. Error latched.
HB10_HS_OL	D3	rc	High-side (HS) switch of half-bridge 10 open load detection
			0 _B No error on HS10 switch (default value)
			1 _B Open load detected on HS10 switch. Error latched.
HB10_LS_OL	D2	rc	Low-side (LS) switch of half-bridge 10 open load detection
			0 _B No error on LS10 switch (default value)
			1 _B Open load detected on LS10 switch. Error latched.
HB9_HS_OL	D1	rc	High-side (HS) switch of half-bridge 9 open load detection
			0 _B No error on HS9 switch (default value)
			$1_{\rm B}$ Open load detected on HS9 switch. Error latched.
HB9_LS_OL	D0	rc	Low-side (LS) switch of half-bridge 9 open load detection
			0 _B No error on LS9 switch (default value)
			$1_{\rm B}$ Open load detected on LS9 switch. Error latched.



8 Application Information

Note: The following simplified application examples are given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device. The function of the described circuits must be verified in the real application.

8.1 Application Diagram

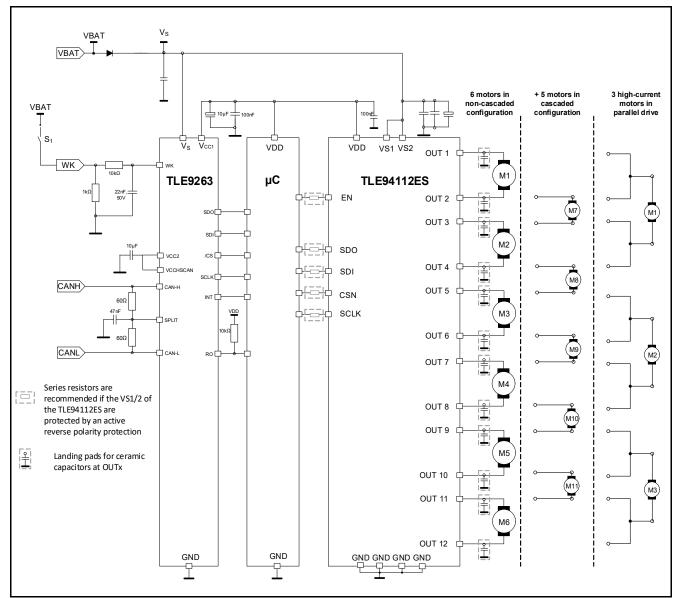


Figure 27 Application example for DC-motor loads



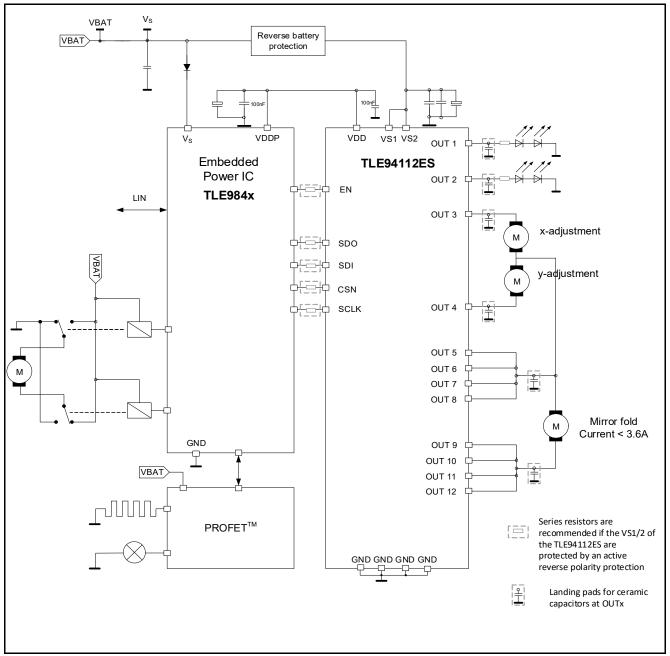


Figure 28 Application example for side mirror control

Notes on the application example

- 1. Series resistors between the microcontroller and the signal pins of the TLE94112ES are recommended if an active reverse polarity protection (MOSFET) is used to protect VS1 and VS2 pins. These resistors limit the current between the microcontroller and the device during negative transients on VBAT (e.g. ISO/TR 7637 pulse 1)
- 2. Landing pads for ceramic capacitors at the outputs of the TLE94112ES as close as possible to the connectors are recommended (the ceramic capacitors are not populated if unused). These ceramic capacitors can be mounted if a higher performance in term of ESD capability is required.
- 3. The electrolytic capacitor at the VSx pins should be dimensioned in order to prevent the VS voltage from exceeding the absolute maximum rating. PWM operation with a too low capacitance can lead to a VS voltage overshoot, which results in a VS overvoltage detection.



- 4. Unused outputs are recommended to be left unconnected (open) in the application. If unused output pins are routed to an external connector which leaves the PCB, then these outputs should have provision for a zero ohm jumper (depopulated if unused) or ESD protection. In other words, unused pins should be treated like used pins.
- 5. Place bypass ceramic capacitors as close as possible to the VSx pins, with shortest connections the GND pins and GND layer, for best EMC performance



8.2 Thermal application information

Ta = 85°C, Ch1 to Ch12 are dissipating a total of 1.62W (0.135W each).

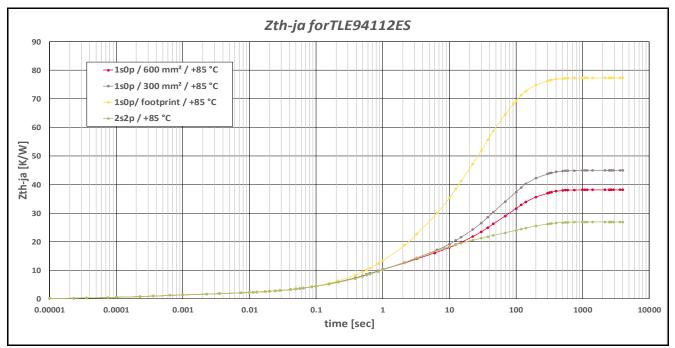


Figure 29 ZthJA Curve for different PCB setups

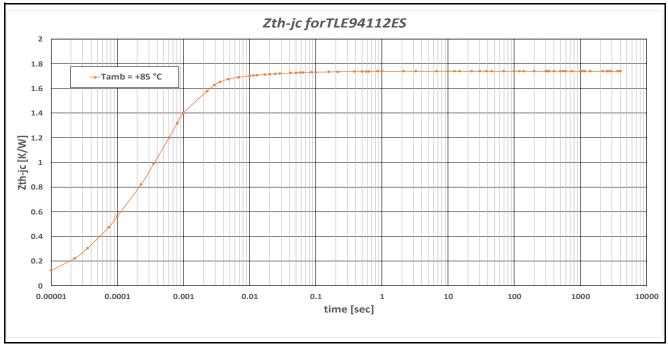


Figure 30 ZthJC Curve



8.3 EMC Enhancement

In the event the emissions of the device exceed the allowable limits, a modulation of the oscillator frequency is incorporated to reduce eventual harmonics of the 8MHz base clock. The frequencies can be selected based on the resolution bandwidth of the peak detector during EMC testing.

The selection is achieved by setting the FM_CLK_MODn bits in the PWM_CH_FREQ_CTRL register as follows:

00_B: OFF 01_B: FM CLK=15.625 kHZ 10_B: FM CLK=31.25 kHz 11_B: FM CLK=62.5 kHz



Package Outlines

9 Package Outlines

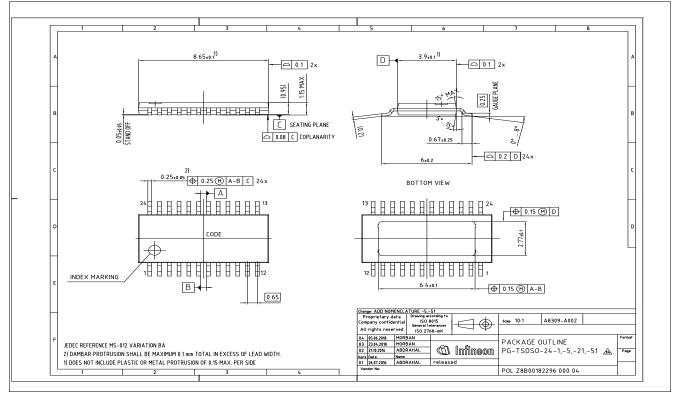


Figure 31 PG-TSDSO-24 (Plastic/Plastic Green - Dual Small Outline Package)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e lead-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).



Revision History

10 Revision History

Revision	Date	Changes
1.0	2020-09-29	Initial release

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